

ECE 536 – Integrated Optics and Optoelectronics
Lecture 9 – February 15, 2022

Spring 2022

Tu-Th 11:00am-12:20pm

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ECE Department, University of Illinois

Lecture 9 Outline

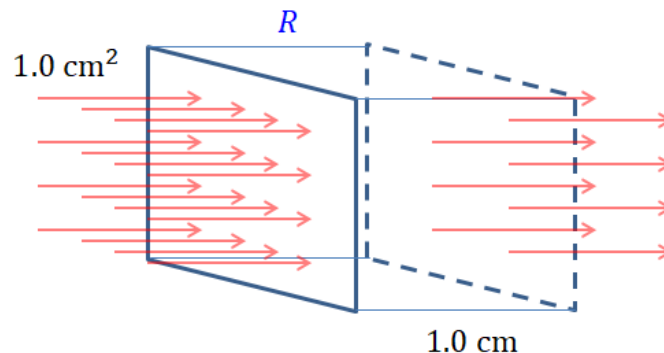
- Optical Absorption
- Optical Gain

Quick Recap – Absorption Coefficient

Net Upward Transition

$$R = \frac{2}{V} \sum_{k_a} \sum_{k_b} \frac{2\pi}{\hbar} |H'_{ba}|^2 \delta(E_b - E_a - \hbar\omega) (f_a - f_b)$$

$$\frac{\text{optical intensity}}{\text{energy per photon}} = \frac{|\langle P \rangle|}{\hbar\omega} = \frac{n_r c \epsilon_0 \omega^2 A_0^2}{2 \hbar\omega}$$



$$\alpha = \frac{R}{(P/\hbar\omega)} = \frac{\hbar\omega}{\left(\frac{n_r c \epsilon_0 \omega^2 A_0^2}{2}\right)} \frac{2}{V} \sum_{k_a} \sum_{k_b} \frac{2\pi}{\hbar} |H'_{ba}|^2 \delta(E_b - E_a - \hbar\omega) (f_a - f_b)$$

Perturbation Hamiltonian

$$H'(\mathbf{r}) = -\frac{eA_o e^{i\mathbf{k}_{op} \cdot \mathbf{r}}}{2m_o} (\hat{\mathbf{e}} \cdot \mathbf{p})$$

Long λ (dipole) Approximation

$$\mathbf{A}(\mathbf{r}) = \mathbf{A} e^{i\mathbf{k}_{op} \cdot \mathbf{r}} \simeq \mathbf{A}$$

$$H'_{ba} \simeq -\frac{e}{m_o} \mathbf{A} \cdot \langle b | \mathbf{p} | a \rangle = -\frac{eA_o}{2m_o} \hat{\mathbf{e}} \cdot \mathbf{p}_{ba}$$

Quick Recap – Absorption Coefficient

$$\alpha = C_o \frac{2}{V} \sum_{k_a} \sum_{k_b} |\hat{e} \cdot \mathbf{p}_{ba}|^2 \delta(E_b - E_a - \hbar\omega) (f_a - f_b)$$

$$C_o = \frac{\pi e^2}{n_r c \epsilon_0 m_0^2 \omega} \quad \mathbf{p}_{ba} = \langle b | \frac{\hbar}{i} \nabla | a \rangle = \int \Psi_b^*(\mathbf{r}) \frac{\hbar}{i} \nabla \Psi_a(\mathbf{r})$$

Expressed in terms of the electric dipole moment

$$\alpha(\hbar\omega) = \frac{\pi\omega}{n_r c \epsilon_0} \frac{2}{V} \sum_{k_a} \sum_{k_b} |\hat{e} \cdot \boldsymbol{\mu}_{ba}|^2 \delta(E_b - E_a - \hbar\omega) (f_a - f_b)$$

$$\boldsymbol{\mu}_{ba} = e \langle b | \mathbf{r} | a \rangle = e \mathbf{r}_{ba}$$

Then we have asked ourselves how to calculate the optical matrix element we have in the net upward transition

$$R = R_{a \rightarrow b} - R_{b \rightarrow a} = \frac{2}{V} \sum_{k_a} \sum_{k_b} \frac{2\pi}{\hbar} |H'_{ba}|^2 \delta(E_b - E_a - \hbar\omega)(f_a - f_b)$$

$$H'_{ba} = \left\langle b \left| \frac{-eA(\mathbf{r})}{m_0} \cdot \mathbf{p} \right| a \right\rangle$$

Vector potential for the optical field

$$\mathbf{A}(\mathbf{r}) = \mathbf{A}e^{i\mathbf{k}_{op} \cdot \mathbf{r}} = \frac{\hat{e}A_0}{2} e^{i\mathbf{k}_{op} \cdot \mathbf{r}}$$

valence band state

$$\psi_a = \frac{u_v(\mathbf{r})e^{i\mathbf{k}_v \cdot \mathbf{r}}}{\sqrt{Vol}}$$

conduction band state

$$\psi_b = \frac{u_c(\mathbf{r})e^{i\mathbf{k}_c \cdot \mathbf{r}}}{\sqrt{Vol}}$$

$$H'_{ba} = -\frac{eA_0}{2m_0} \hat{e} \cdot \int \frac{u_c^*(\mathbf{r})e^{-i\mathbf{k}_c \cdot \mathbf{r}}}{\sqrt{Vol}} e^{i\mathbf{k}_{op} \cdot \mathbf{r}} (-i\hbar\nabla) \frac{u_v(\mathbf{r})e^{i\mathbf{k}_v \cdot \mathbf{r}}}{\sqrt{Vol}} d^3\mathbf{r}$$

Then we have asked ourselves how to calculate the optical matrix element we have in the net upward transition

$$R = R_{a \rightarrow b} - R_{b \rightarrow a} = \frac{2}{V} \sum_{k_a} \sum_{k_b} \frac{2\pi}{\hbar} |H'_{ba}|^2 \delta(E_b - E_a - \hbar\omega)(f_a - f_b)$$

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$$H'_{ba} = -\frac{eA_0}{2m_0} \hat{e} \cdot \int \frac{u_c^*(\mathbf{r}) e^{-i\mathbf{k}_c \cdot \mathbf{r}}}{\sqrt{Vol}} e^{i\mathbf{k}_{op} \cdot \mathbf{r}} (-i\hbar \nabla) \frac{u_v(\mathbf{r}) e^{i\mathbf{k}_v \cdot \mathbf{r}}}{\sqrt{Vol}} d^3\mathbf{r}$$

$$e^{-i\mathbf{k}_c \cdot \mathbf{r}}$$

slowly varying
over a unit cell

$$e^{i\mathbf{k}_v \cdot \mathbf{r}}$$

$$u_c^*(\mathbf{r}) (-i\hbar \nabla u_v(\mathbf{r}))$$

$$u_c^*(\mathbf{r}) u_v(\mathbf{r})$$

fast varying
over a unit cell

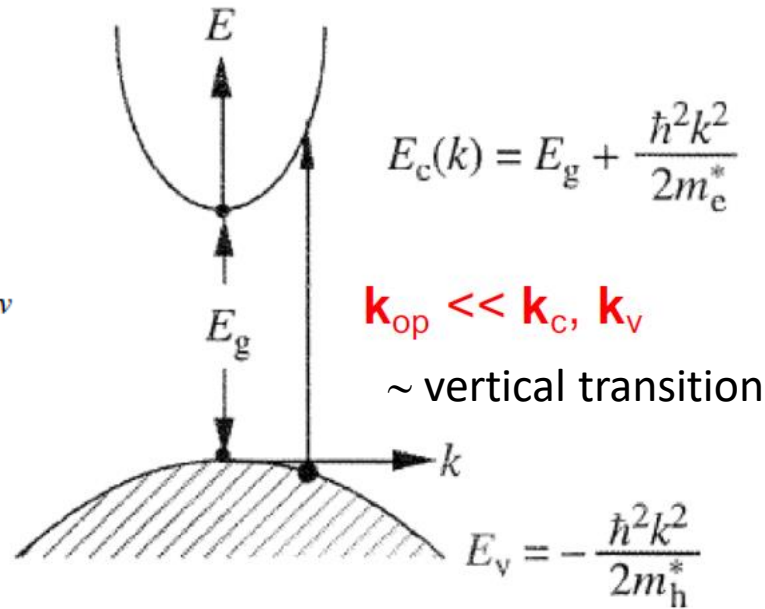
We separated the integral into the product of two integrals

$$\begin{aligned}
 H'_{ba} &\simeq -\frac{eA_0}{2m_0} \hat{e} \cdot \int_{\Omega} u_c^*(r) (-i\hbar \nabla u_v(r)) \frac{d^3r}{\Omega} \int_V e^{i(-k_c+k_v+k_{op})\cdot r} \frac{d^3r}{V} + 0 \\
 &= -\frac{eA_0}{2m_0} \hat{e} \cdot \mathbf{p}_{cv} \delta(k_c, k_v + k_{op})
 \end{aligned}$$

$$\mathbf{p}_{cv} = \int_{\Omega} u_c^*(r) (-i\hbar \nabla u_v(r)) \frac{d^3r}{\Omega}$$

k-selection Rule

$$H'_{ba} \simeq -\frac{eA_0}{2m_0} \hat{e} \cdot \mathbf{p}_{cv} \delta_{\mathbf{k}_c, \mathbf{k}_v}$$



$$E_c - E_v = E_g + \frac{\hbar^2 k^2}{2m_e^*} + \frac{\hbar^2 k^2}{2m_h^*} = E_g + \frac{\hbar^2 k^2}{2m_r^*}$$

$$\frac{1}{m_r^*} = \frac{1}{m_e^*} + \frac{1}{m_h^*}$$

Optical Absorption Spectrum

$$\begin{aligned}
 \alpha(\hbar\omega) &= \frac{\hbar\omega}{\left(\frac{n_r c \epsilon_o \omega^2 A_o^2}{2}\right)} \frac{2}{V} \sum_{k_a} \sum_{k_b} \frac{2\pi}{\hbar} |H'_{ba}|^2 \delta(E_b - E_a - \hbar\omega) (f_a - f_b) \\
 &= \frac{\hbar\omega}{\left(\frac{n_r c \epsilon_o \omega^2 A_o^2}{2}\right)} \frac{2}{V} \sum_{k_v} \sum_{k_c} \frac{2\pi}{\hbar} \left| \frac{-eA_o}{2m_o} \hat{e} \cdot \mathbf{p}_{cv} \delta_{\mathbf{k}_c, \mathbf{k}_v} \right|^2 \delta(E_c - E_v - \hbar\omega) (f_v - f_c) \\
 &= \frac{\pi e^2}{n_r c \epsilon_o m_o^2 \omega} \frac{2}{V} \sum_{k_v} \sum_{k_c} |\hat{e} \cdot \mathbf{p}_{cv}|^2 \delta_{\mathbf{k}_c, \mathbf{k}_v} \delta(E_c - E_v - \hbar\omega) (f_v - f_c) \\
 &= C_o \frac{2}{V} \sum_{\mathbf{k}} |\hat{e} \cdot \mathbf{p}_{cv}|^2 \delta(E_c - E_v - \hbar\omega) (f_v(\mathbf{k}) - f_c(\mathbf{k}))
 \end{aligned}$$

k represents both \mathbf{k}_c and \mathbf{k}_v
 They are equal by the k-selection rule

Optical Absorption Spectrum

Starting with the general expression

$$\alpha(\hbar\omega) = C_o \frac{2}{V} \sum_{\mathbf{k}} |\hat{\mathbf{e}} \cdot \mathbf{p}_{cv}|^2 \delta(E_c - E_v - \hbar\omega) (f_v - f_c)$$

we assume an undoped bulk material in thermal equilibrium, with valence band fully occupied and conduction band completely empty

$$E_c = E_v = E_F \qquad f_v = 1 \qquad f_c = 0$$

$$\alpha_0(\hbar\omega) = C_0 |\hat{\mathbf{e}} \cdot \mathbf{p}_{cv}|^2 \int \frac{2d^2k}{(2\pi)^3} \delta\left(E_g + \frac{\hbar^2 k^2}{2m_r} - \hbar\omega\right)$$

$$\frac{1}{m_r^*} = \frac{1}{m_e^*} + \frac{1}{m_h^*}$$

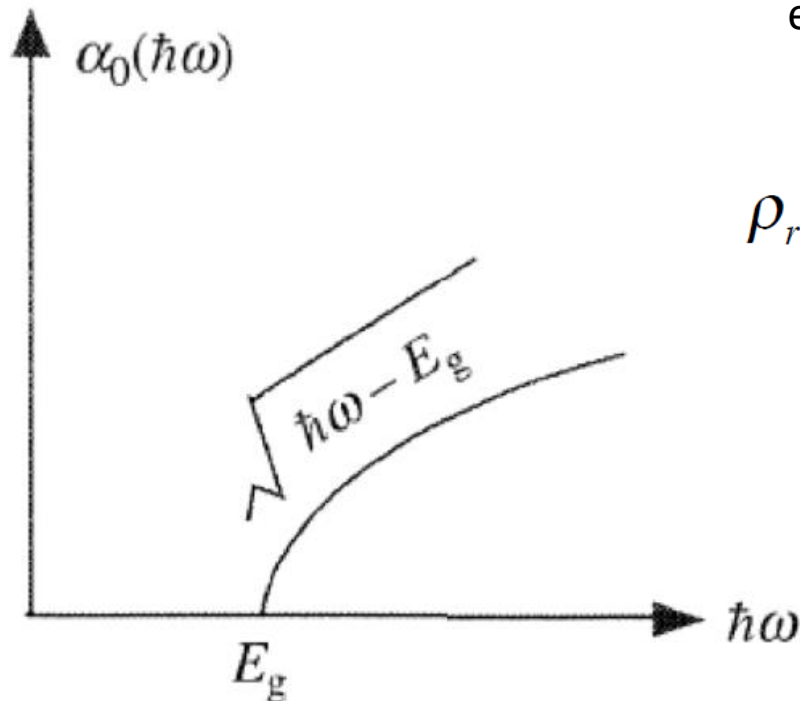
Optical Absorption Spectrum

The integral can be solved analytically arriving at the **bulk absorption coefficient**

$$\alpha_o(\hbar\omega) = C_o \underbrace{|\hat{e} \cdot \mathbf{p}_{cv}|^2}_{\text{momentum matrix element}} \underbrace{\rho_r(\hbar\omega - E_g)}_{\text{joint (reduced) density of states}}$$

momentum matrix
element

joint (reduced) density of states



$$\rho_r(\hbar\omega - E_g) = \frac{1}{2\pi^2} \left(\frac{2m_r^*}{\hbar^2} \right)^{3/2} (\hbar\omega - E_g)^{1/2}$$

$$\frac{1}{m_r^*} = \frac{1}{m_e^*} + \frac{1}{m_h^*}$$

Optical Gain Spectra (with carriers)

Under current injection or optical pumping, we have quasi-Fermi levels F_c and F_v

$$\alpha(\hbar\omega) = C_o \frac{2}{V} \sum_k |\hat{e} \cdot \mathbf{p}_{cv}|^2 \delta(E_c - E_v - \hbar\omega) (f_v(\mathbf{k}) - f_c(\mathbf{k}))$$

$$f_v(\mathbf{k}) = \frac{1}{1 + e^{(E_v(\mathbf{k}) - F_v)/kT}} \quad f_c(\mathbf{k}) = \frac{1}{1 + e^{(E_c(\mathbf{k}) - F_c)/kT}}$$

We carry out the integral as before

$$\alpha(\hbar\omega) = C_0 |\hat{e} \cdot \mathbf{p}_{cv}|^2 \int \frac{2d^2k}{(2\pi)^3} \delta\left(E_g + \frac{\hbar^2 k^2}{2m_r} - \hbar\omega\right) [f_v(k) - f_c(k)]$$

Optical Gain Spectra (with carriers)

$$\alpha(\hbar\omega) = C_0 |\hat{e} \cdot \mathbf{p}_{cv}|^2 \int \frac{2d^2k}{(2\pi)^3} \delta\left(E_g + \frac{\hbar^2 k^2}{2m_r} - \hbar\omega\right) [f_v(k) - f_c(k)]$$



$$\alpha(\hbar\omega) = \alpha_0(\hbar\omega) (f_v(\mathbf{k}_0) - f_c(\mathbf{k}_0))$$

$$|\mathbf{k}| = \sqrt{\frac{2m_r^*}{\hbar^2} (\hbar\omega - E_g)} \equiv \mathbf{k}_0$$

Optical Gain Spectra (with carriers)

$$\alpha(\hbar\omega) = \alpha_0(\hbar\omega) \left(f_v(\mathbf{k}_0) - f_c(\mathbf{k}_0) \right)$$

We have **Gain** (negative absorption) when

$$f_v(\mathbf{k}_0) < f_c(\mathbf{k}_0)$$



$$E_g < \hbar\omega < F_c - F_v$$

$$F_c - F_v > E_c - E_v = \hbar\omega$$

**population inversion condition
(Bernard-Duraffourg condition)**

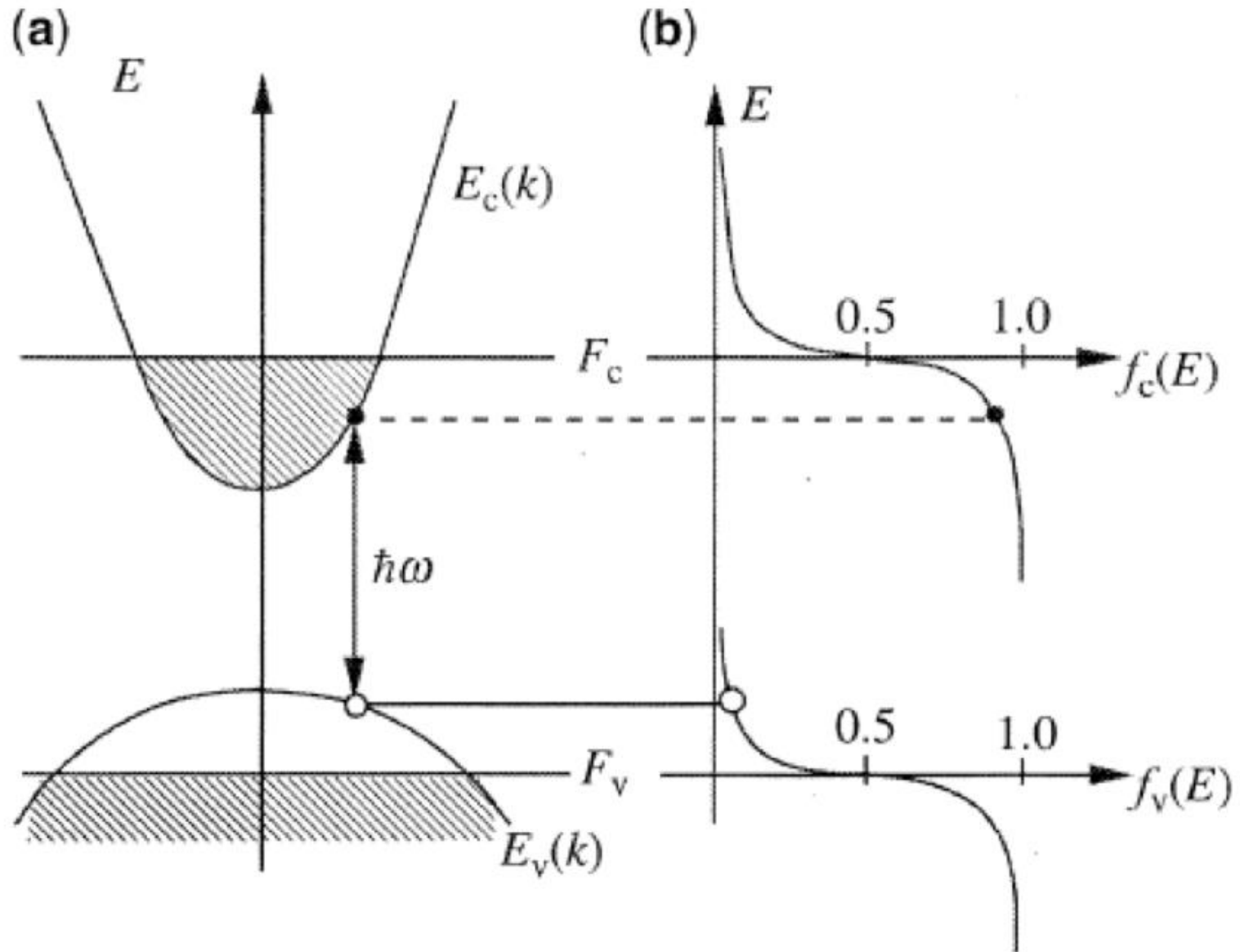
Optical Gain Spectra (with carriers)

The magnitude of the loss (or gain) depends on wavelength. **If the separation of the quasi-Fermi levels is greater than the band gap, there is gain.**

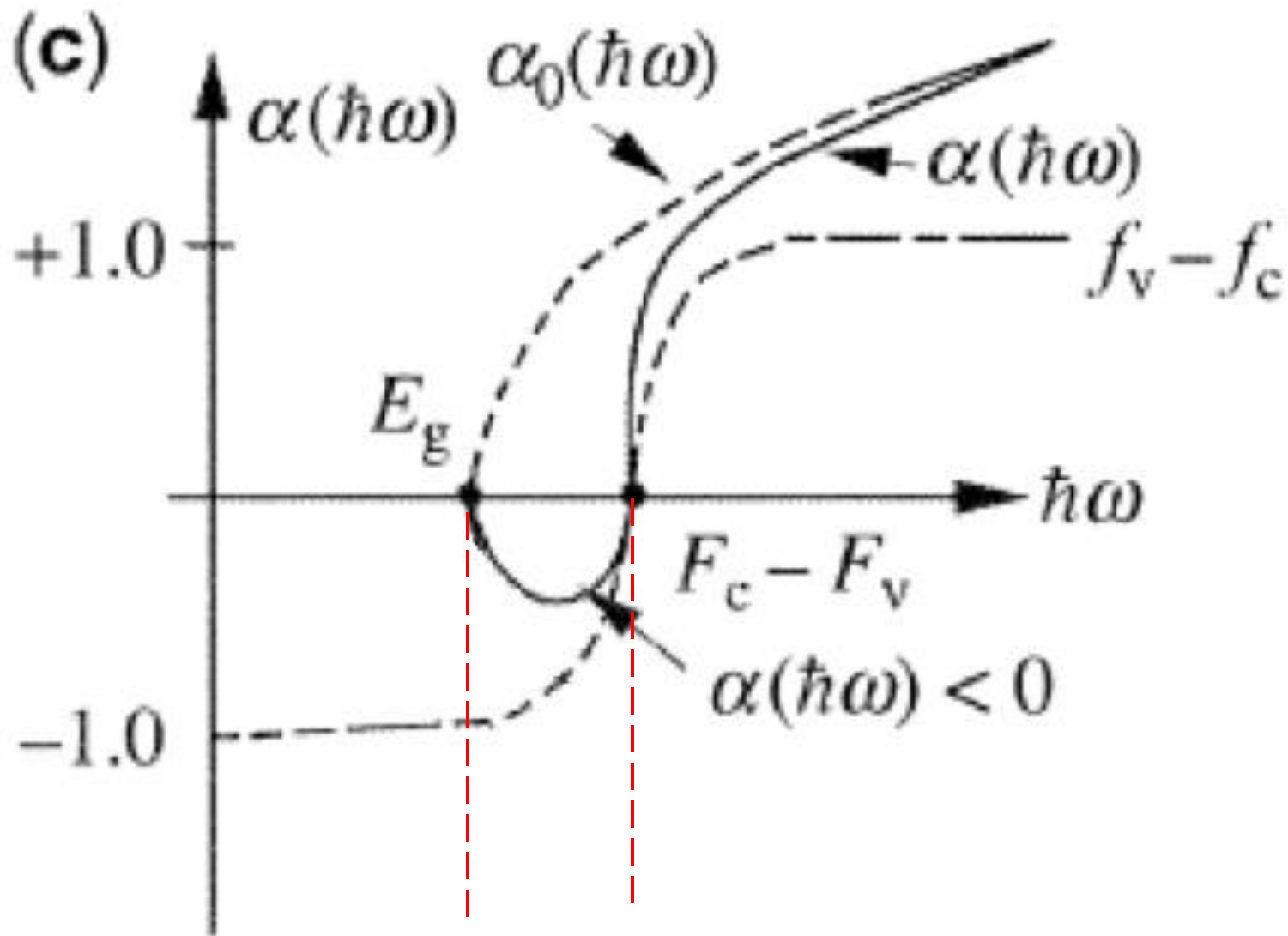
- Photons with energies greater than the bandgap but less than the energy separation of the quasi-Fermi levels will experience gain
- Photons with energies greater than the separation of the quasi-Fermi levels will experience loss

Gain condition $F_C - F_V > \hbar\omega > \underbrace{E_C - E_V}_{E_g}$

Optical Gain Spectra (with carriers)



Optical Gain Spectra (with carriers)



Interband Absorption and Gain in Quantum Well

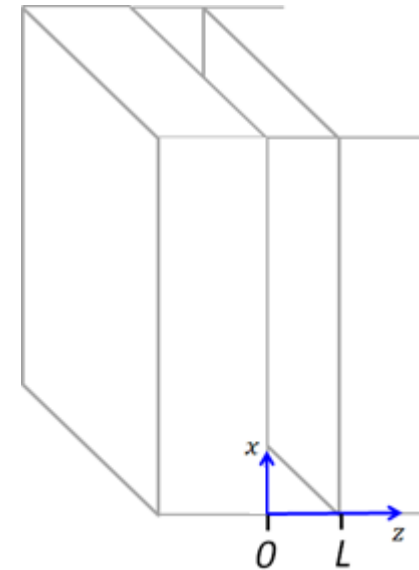
Simple square well potential (infinite barrier)

Consider a 1D well in 3D space quantized along z- axis

$$\left[-\frac{\hbar^2}{2m} \nabla^2 + V(z) \right] \psi(x, y, z) = E \psi(x, y, z)$$

$$\psi_n(x, y, z) = 0$$

$$z \leq 0, z \geq L$$



$$\psi_n(x, y, z) = \underbrace{\frac{e^{ik_x x + ik_y y}}{\sqrt{A}}}_{\text{plane wave}} \underbrace{\sqrt{\frac{2}{L}} \sin\left(\frac{n\pi}{L} z\right)}_{\phi_n(z)}$$

$$0 < z < L$$

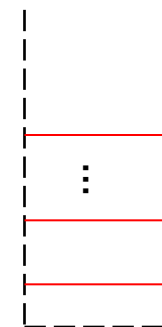
$$n = 1, 2, 3, \dots$$

area in (x,y) plane

well width

$$E_n = \frac{\hbar^2}{2m^*} \left(k_x^2 + k_y^2 + \left(\frac{n\pi}{L} \right)^2 \right)$$

$$k_z = \frac{n\pi}{L}$$



$E_1 \dots E_N$

2-band model – we need to add the valence band

$$\psi_b(\mathbf{r}) = u_c(\mathbf{r}) \frac{e^{i\mathbf{k}'_t \cdot \boldsymbol{\rho}}}{\sqrt{A}} \phi_n(z)$$

$$|\boldsymbol{\rho}| = \sqrt{x^2 + y^2}$$

\mathbf{k}'_t = transverse momentum for electrons

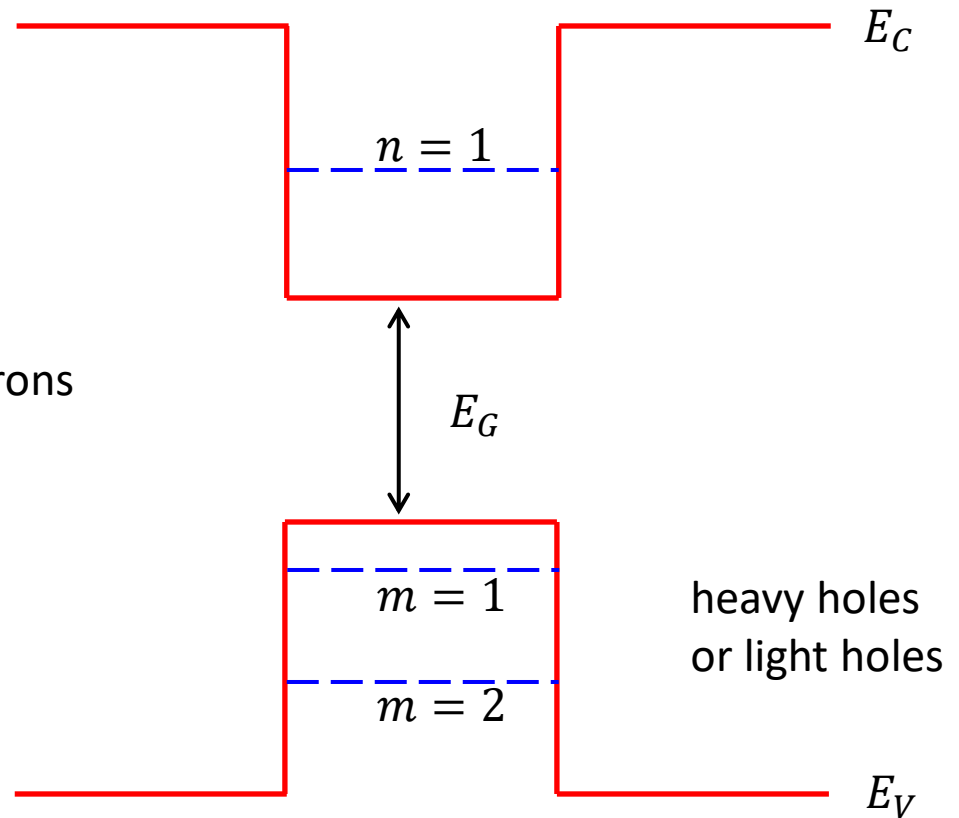
\mathbf{k}_t = transverse momentum for holes

$$\psi_a(\mathbf{r}) = u_v(\mathbf{r}) \frac{e^{i\mathbf{k}_t \cdot \boldsymbol{\rho}}}{\sqrt{A}} g_m(z)$$

periodic Bloch wave

plane wave on (x,y) plane

quantized envelope wavefunction



Interband Absorption and Gain in Quantum Well

(We neglect here exciton interactions between electrons and holes)

Starting with the general expression for the absorption coefficient

$$\alpha(\hbar\omega) = C_o \frac{2}{V} \sum_{\mathbf{k}_a} \sum_{\mathbf{k}_b} |\hat{\mathbf{e}} \cdot \mathbf{p}_{ba}|^2 \delta(E_b - E_a - \hbar\omega) (f_a - f_b)$$

$$\mathbf{p}_{ba} = \langle \psi_b | \mathbf{p} | \psi_a \rangle = \int \psi_b^* \frac{\hbar}{i} \nabla \psi_a d^3 \mathbf{r}$$

$$= \int u_c^*(\mathbf{r}) \frac{e^{-i\mathbf{k}'_t \cdot \mathbf{r}}}{\sqrt{A}} \phi_n^*(z) \frac{\hbar}{i} \nabla \left(u_v(\mathbf{r}) \frac{e^{i\mathbf{k}_t \cdot \mathbf{r}}}{\sqrt{A}} g_m(z) \right) d^3 \mathbf{r}$$

$$\mathbf{p}_{ba} = \langle \psi_b | \mathbf{p} | \psi_a \rangle = \int \Psi_b^* \frac{\hbar}{i} \nabla \Psi_a d^3 \mathbf{r}$$

$$= \int u_c^*(\mathbf{r}) \frac{e^{-i\mathbf{k}'_t \cdot \mathbf{r}}}{\sqrt{A}} \phi_n^*(z) \frac{\hbar}{i} \nabla \left(u_v(\mathbf{r}) \frac{e^{i\mathbf{k}_t \cdot \mathbf{r}}}{\sqrt{A}} g_m(z) \right) d^3 \mathbf{r}$$

$$= \frac{\hbar}{iA} \int u_c^*(\mathbf{r}) e^{-i\mathbf{k}'_t \cdot \mathbf{r}} \phi_n^*(z) \left[e^{i\mathbf{k}_t \cdot \mathbf{r}} g_m(z) \nabla u_v(\mathbf{r}) + u_v(\mathbf{r}) g_m(z) \nabla e^{i\mathbf{k}_t \cdot \mathbf{r}} + u_v(\mathbf{r}) e^{i\mathbf{k}_t \cdot \mathbf{r}} \nabla g_m(z) \right] d^3 \mathbf{r}$$

$$= \frac{\hbar}{iA} \int \underbrace{u_c^*(\mathbf{r}) \nabla u_v(\mathbf{r})}_{\approx \langle u_c | \mathbf{p} | u_v \rangle} \underbrace{e^{-i\mathbf{k}'_t \cdot \mathbf{r}} e^{i\mathbf{k}_t \cdot \mathbf{r}}}_{\delta_{\mathbf{k}_t, \mathbf{k}'_t}} \underbrace{\phi_n^*(z) g_m(z)}_{\mathbf{I}_{hm}^{en}} + \dots$$

$$\approx \langle u_c | \mathbf{p} | u_v \rangle \delta_{\mathbf{k}_t, \mathbf{k}'_t} \mathbf{I}_{hm}^{en}$$

$$\mathbf{p}_{ba} \approx \langle u_c | \mathbf{p} | u_v \rangle \delta_{\mathbf{k}_t, \mathbf{k}'_t} \mathbf{I}_{hm}^{en}$$

\mathbf{p}_{cv}
 \mathbf{k} -selection rule $\rightarrow \mathbf{k}_t = \mathbf{k}'_t$
conservation of transverse momentum from exponentials


electron state n
 hole state m
 overlap integral of quantized wavefunctions in well

$$\mathbf{I}_{hm}^{en} = \int_{-\infty}^{\infty} \phi_n^*(z) g_m(z) dz$$


overlap integral

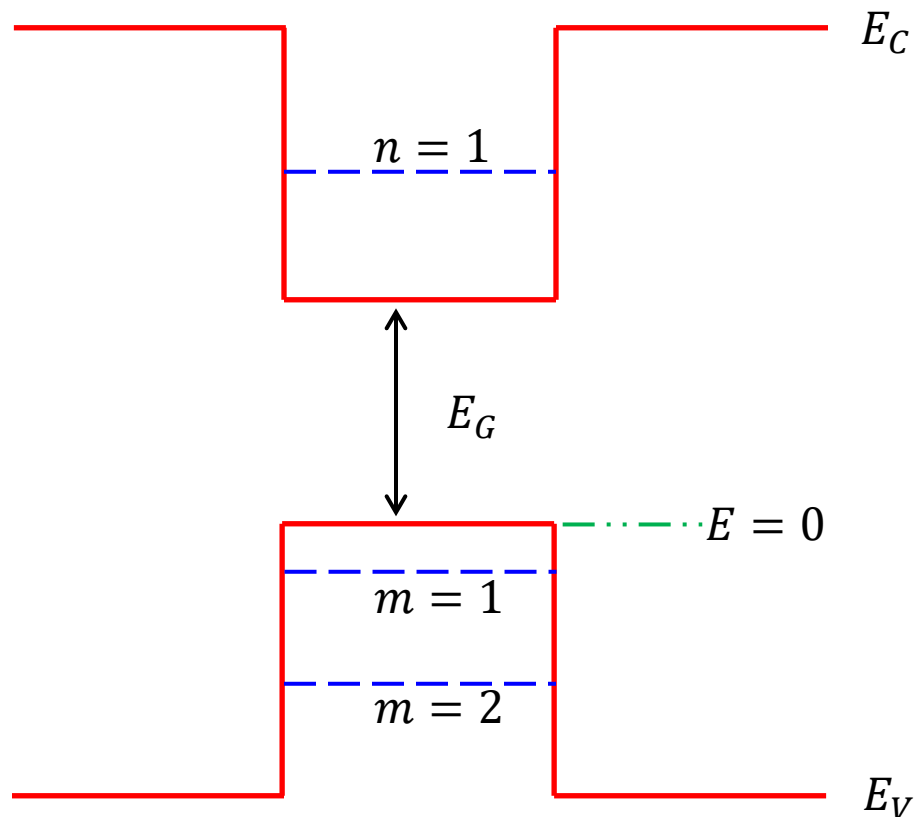
Transition energies (all are relative to top of valence band)

$$E_b = E_g + E_{en} + \frac{\hbar^2 k_t^2}{2m_e^*}$$


 Energy level of electron state

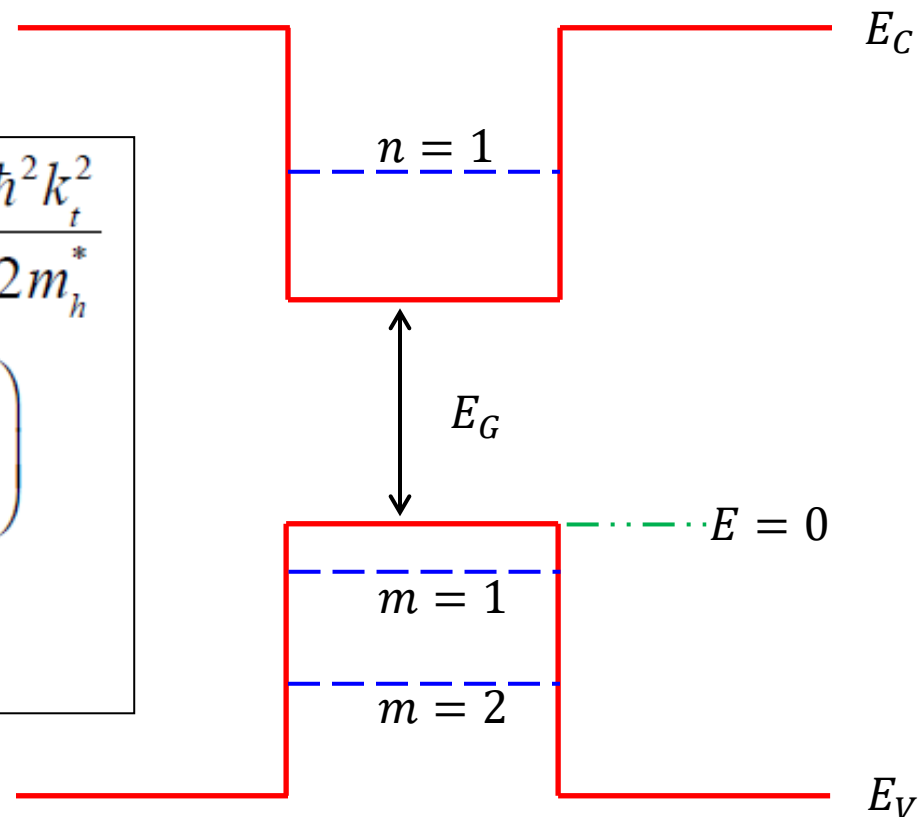
$$E_a = E_{hm} - \frac{\hbar^2 k_t^2}{2m_h^*}$$


 Energy level of hole state
 (NOTE: it's negative)



Transition energies (all are relative to top of valence band)

$$\begin{aligned}
 E_b - E_a &= E_g + E_{en} + \frac{\hbar^2 k_t^2}{2m_e^*} - E_{hm} + \frac{\hbar^2 k_t^2}{2m_h^*} \\
 &= \left(E_g + E_{en} - E_{hm} \right) + \left(\frac{\hbar^2 k_t^2}{2m_h^*} + \frac{\hbar^2 k_t^2}{2m_e^*} \right) \\
 &= E_{hm}^{en} + E_t
 \end{aligned}$$



$$E_{hm}^{en} = E_g + E_{en} - E_{hm}$$

Band edge transition energy

$$E_t = \frac{\hbar^2 k_t^2}{2m_r^*}$$

Transverse kinetic energy due to in-plane k-vector

$$\frac{1}{m_r^*} = \frac{1}{m_e^*} + \frac{1}{m_h^*}$$

Absorption expression for quantum well case

$$\alpha(\hbar\omega) = C_o \frac{2}{V} \sum_{\mathbf{k}_a} \sum_{\mathbf{k}_b} |\hat{\mathbf{e}} \cdot \mathbf{p}_{ba}|^2 \delta(E_b - E_a - \hbar\omega) (f_a - f_b)$$

- Summations over \mathbf{k}_a and \mathbf{k}_b become summations over \mathbf{k}_t and \mathbf{k}'_t
- The k-selection rule establishes $\mathbf{k}_t = \mathbf{k}'_t$ so the sum becomes a sum over \mathbf{k}_t
- We need to sum also over m and n

$$\alpha(\hbar\omega) = C_o \sum_{n,m} |I_{hm}^{en}|^2 \frac{2}{V} \sum_{\mathbf{k}_t} |\hat{\mathbf{e}} \cdot \mathbf{p}_{cv}|^2 \delta(E_{hm}^{en} + E_t - \hbar\omega) (f_v^m - f_c^n)$$

Joint Density of States

$$\frac{2}{V} \sum_{\mathbf{k}_t} = \frac{2}{V} \int \frac{d^2 \mathbf{k}_t}{\left(\frac{2\pi}{L}\right)^2} = \frac{2A}{V} \int \frac{d^2 \mathbf{k}_t}{(2\pi)^2} = \frac{1}{\pi L_z} \int_0^\infty k_t dk_t = \int_0^\infty \rho_r^{2D} dE_t$$

$$E_t = \frac{\hbar^2 k_t^2}{2m_r^*} \rightarrow dE_t = \frac{\hbar^2}{m_r^*} k_t dk_t \rightarrow k_t dk_t = \frac{m_r^*}{\hbar^2} dE_t \rightarrow \rho_r^{2D} = \frac{m_r^*}{\pi \hbar^2 L_z}$$

For an unpumped semiconductor in thermal equilibrium $f_v^m = 1$ $f_c^n = 0$

$$\alpha(\hbar\omega) = C_0 \sum_{m,n} |I_{hm}^{en}|^2 |\hat{e} \cdot \mathbf{p}_{cv}|^2 \int_0^\infty \rho_r^{2D} \delta(E_{hm}^{en} + E_t - \hbar\omega) (f_v^m - f_c^n) dE_t$$

$$\alpha_0(\hbar\omega) = C_0 \sum_{m,n} |I_{hm}^{en}|^2 |\hat{e} \cdot \mathbf{p}_{cv}|^2 \rho_r^{2D} H(\hbar\omega - E_{hm}^{en})$$

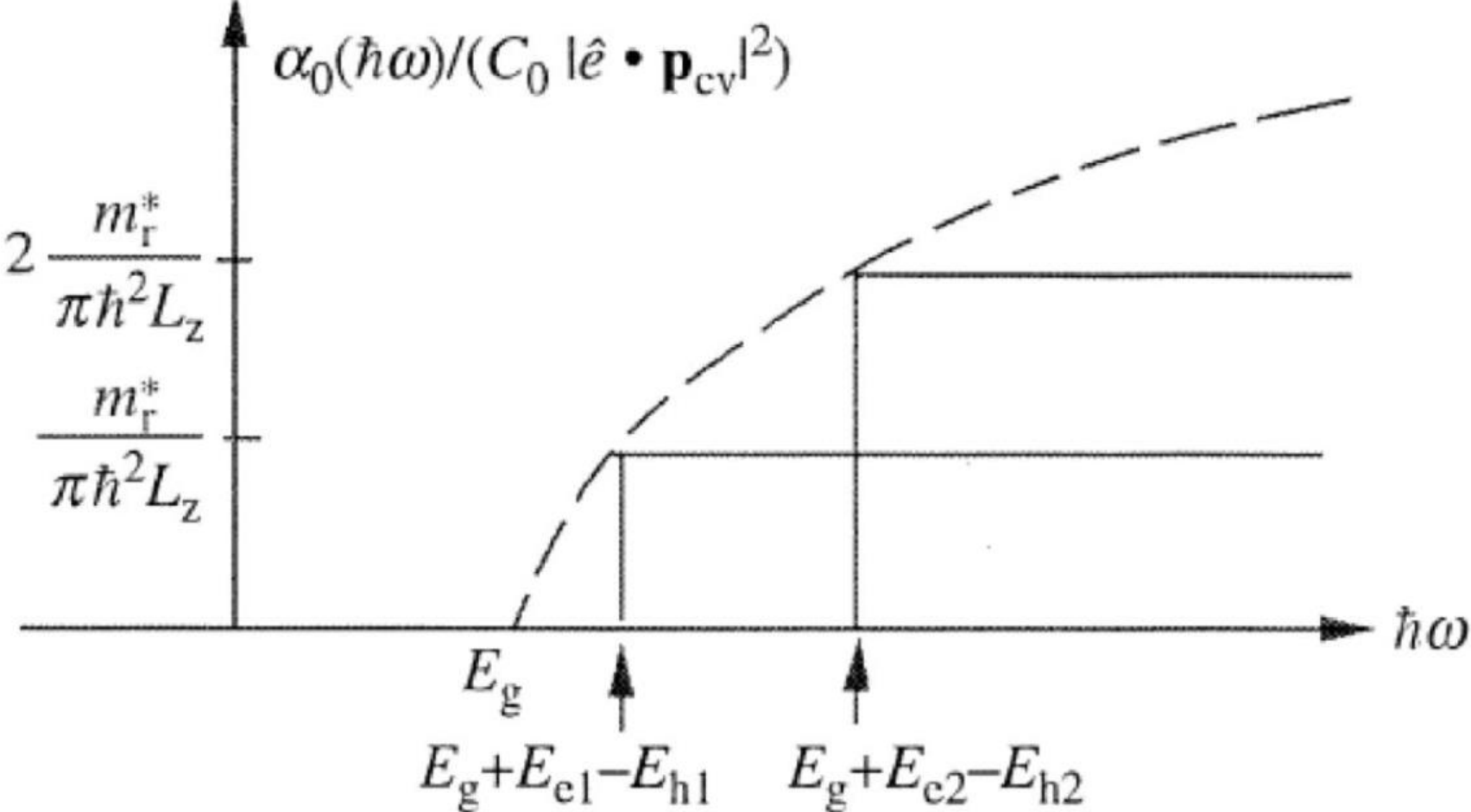
Optical Absorption Spectrum

$$\alpha_0(\hbar\omega) = C_0 |\hat{e} \cdot \mathbf{p}_{cv}|^2 \begin{cases} \frac{m_r^*}{\pi \hbar^2 L_z} & \text{for } E_{h1}^{e1} < \hbar\omega < E_{h2}^{e2} \\ 2 \frac{m_r^*}{\pi \hbar^2 L_z} & \text{for } E_{h2}^{e2} < \hbar\omega < E_{h3}^{e3} \\ 3 \frac{m_r^*}{\pi \hbar^2 L_z} & \text{for } E_{h3}^{e3} < \hbar\omega < E_{h4}^{e4} \\ \text{etc} \end{cases}$$

For the case of carrier injection

$$\begin{aligned} \alpha(\hbar\omega) &= \alpha_0(\hbar\omega) \left[f_v^m(\hbar\omega - E_{hm}^{en}) - f_c^n(\hbar\omega - E_{hm}^{en}) \right] \\ &= \alpha_0(\hbar\omega) \left[f_v^m(E_t) - f_c^n(E_t) \right] \end{aligned}$$

Optical Absorption Spectrum



Reading Assignments:

Sections 9.3 and 9.4 of Chuang's book

Electron Quasi Fermi Levels (when “ n ” electrons have been injected)

$$n = \sum_{\substack{n\text{-occupied} \\ \text{subbands}}} N_n = \sum_n \int_0^{\infty} \rho_e^{2D}(E) f_c^n(E) dE$$

$$N_n = \int_0^{\infty} \rho_e^{2D}(E) f_c^n(E) dE = \frac{m_e^*}{\pi \hbar^2 L_z} \int_{E_{en}}^{\infty} f_c^n(E) dE$$

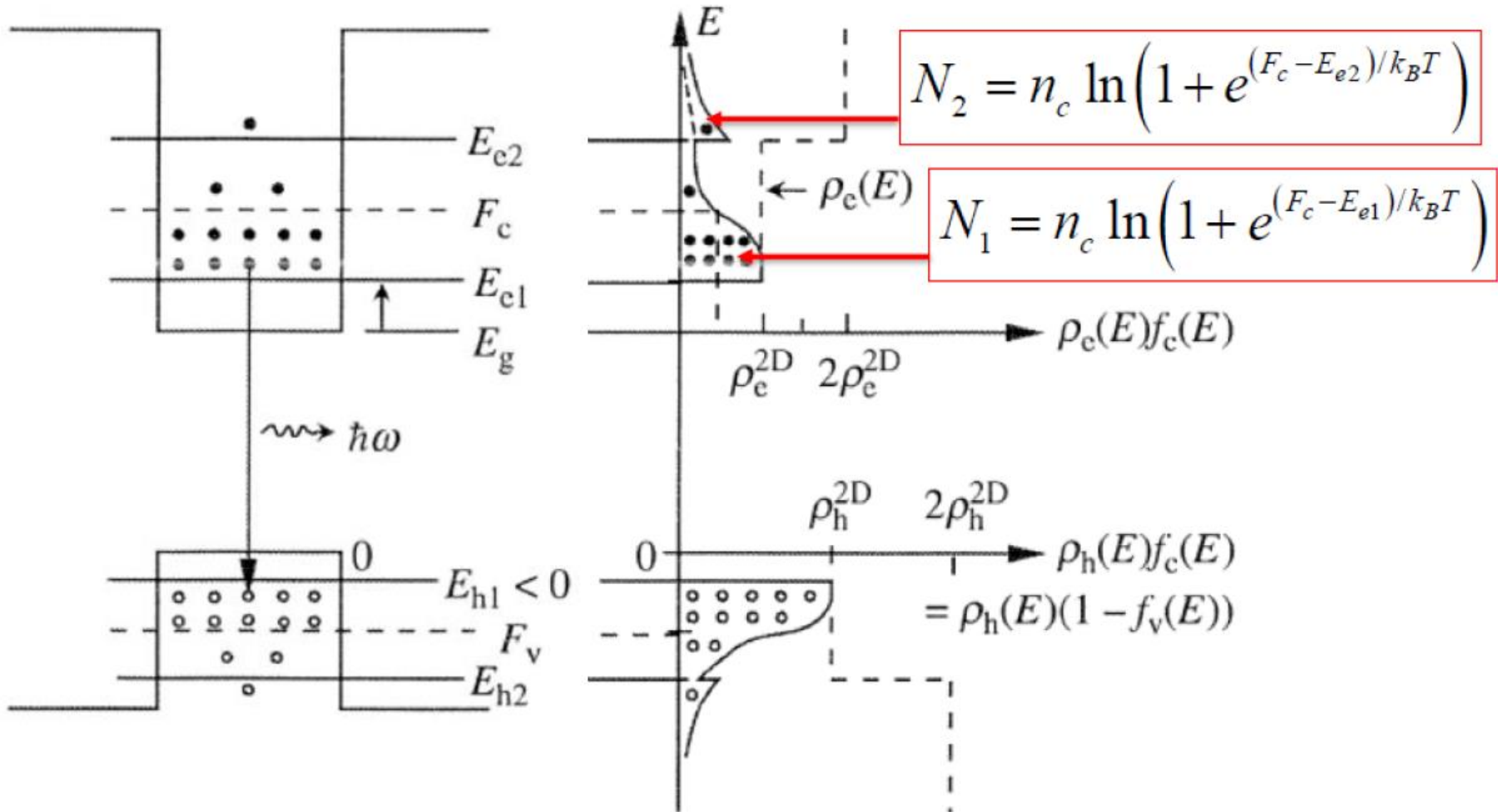
$$\int_{E_{en}}^{\infty} f_c^n(E) dE = \int_{E_{en}}^{\infty} \frac{1}{1 + e^{(E-F_c)/k_B T}} dE = -k_B T \ln \left(1 + e^{(F_c-E)/k_B T} \right) \Bigg|_{E_{en}}^{\infty}$$

$$N_n = \frac{m_e^* k_B T}{\pi \hbar^2 L_z} \ln \left(1 + e^{(F_c-E_{en})/k_B T} \right) = n_c \ln \left(1 + e^{(F_c-E_{en})/k_B T} \right)$$

Electron Quasi Fermi Levels (when “n” electrons have been injected)

$$N_n = n_c \ln\left(1 + e^{(F_c - E_{en})/k_B T}\right)$$

$$n_c = \frac{m_e^* k_B T}{\pi \hbar^2 L_z}$$



Holes Quasi Fermi level (when “p” holes have been injected)

$$E_a = E_{hm} - \frac{\hbar^2 k_t^2}{2m_h^*} \quad \text{where } E_{hm} < 0$$

$$E_{t,h} = -\frac{\hbar^2 k_t^2}{2m_h^*} \quad dE_t = -\frac{\hbar^2}{m_h^*} k_t dk_t$$

$$\frac{2}{V} \sum_{\mathbf{k}_t} = \frac{2}{V} \int \frac{d^2 \mathbf{k}_t}{\left(\frac{2\pi}{L}\right)^2} = \frac{2A}{V} \int \frac{d^2 \mathbf{k}_t}{(2\pi)^2} = \frac{1}{\pi L_z} \int_0^\infty k_t dk_t$$

$$= -\int_0^{-\infty} \rho_h^{2D} dE_{t,h} = \int_{-\infty}^0 \rho_h^{2D} dE_{t,h}$$

Holes Quasi Fermi level (when “p” holes have been injected)

$$p = n + N_A^- - N_D^+ = \sum_{\text{occupied subbands}} P_m = \sum_{\text{occupied subbands}} \int_{-\infty}^0 \rho_h^{2D}(E) [1 - f_v^m(E)] dE$$

$$P_m = \int_{-\infty}^0 \rho_h^{2D}(E) f_h^m(E) dE = \frac{m_h^*}{\pi \hbar^2 L_z} \int_{-\infty}^{E_{hm}} f_h^m(E) dE$$

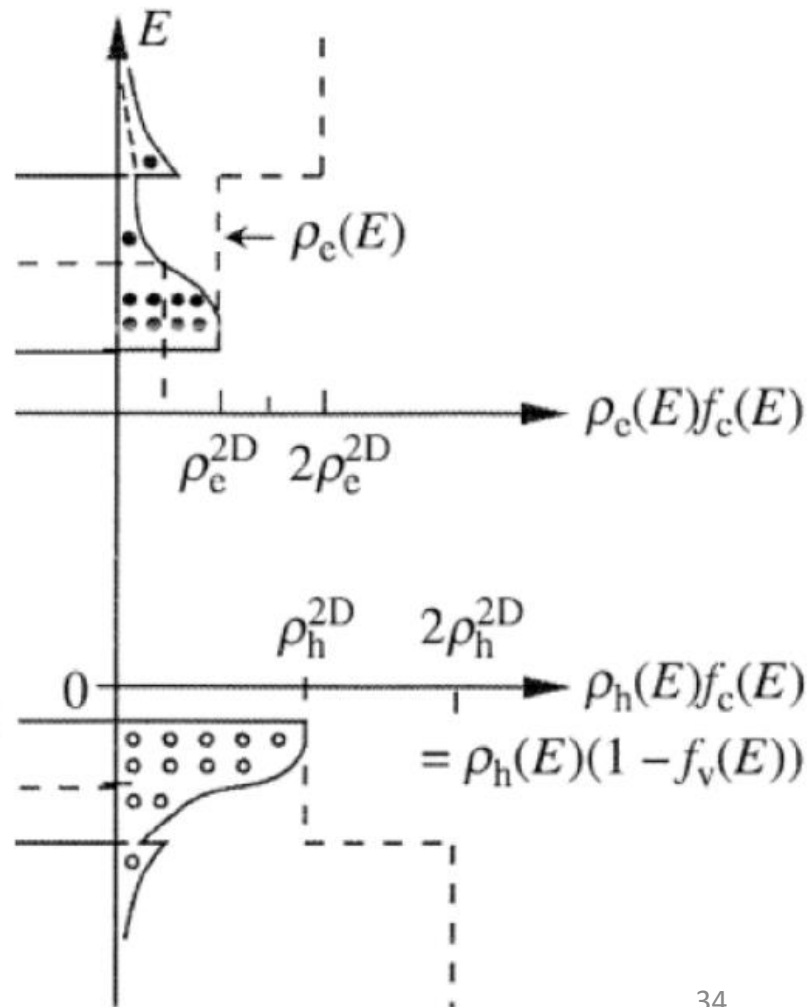
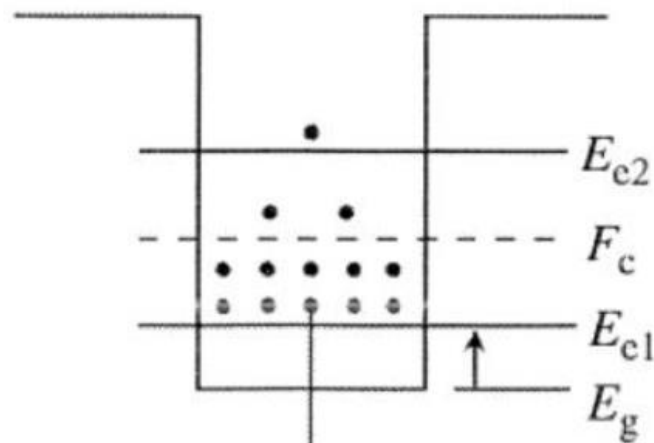
$$\int_{-\infty}^{E_{hm}} f_h^m(E) dE = \int_{-\infty}^{E_{hm}} \frac{1}{1 + e^{-(E - F_v)/k_B T}} dE = k_B T \ln \left(1 + e^{(E_{hm} - F_v)/k_B T} \right) \Big|_{-\infty}^{E_{hm}}$$

$$P_m = \frac{m_h^* k_B T}{\pi \hbar^2 L_z} \ln \left(1 + e^{(E_{hm} - F_v)/k_B T} \right) = n_v \ln \left(1 + e^{(E_{hm} - F_v)/k_B T} \right)$$

Holes Quasi Fermi level (when "p" holes have been injected)

$$P_m = n_v \ln\left(1 + e^{(E_{hm} - F_v)/k_B T}\right)$$

$$n_v = \frac{m_h^* k_B T}{\pi \hbar^2 L_z}$$



$$P_1 = n_v \ln\left(1 + e^{(E_{h1} - F_v)/k_B T}\right)$$

$$P_2 = n_v \ln\left(1 + e^{(E_{h2} - F_v)/k_B T}\right)$$

Gain Spectrum

Zero Linewidth Case:

$$g(\hbar\omega) = C_0 \sum_{m,n} |I_{hm}^{en}|^2 |\hat{e} \cdot \mathbf{p}_{cv}|^2 [f_c^n(E_t) - f_v^m(E_t)] \rho_r^{2D} H(\hbar\omega - E_{hm}^{en})$$

$$C_0 = \frac{\pi e^2}{n_r c \epsilon_0 m_0^2 \omega}$$

$$I_{hm}^{en} = \int_{-\infty}^{\infty} \phi_n^*(z) g_m(z) dz$$

$$\rho_r^{2D} = \frac{m_r^*}{\pi \hbar^2 L_z}$$

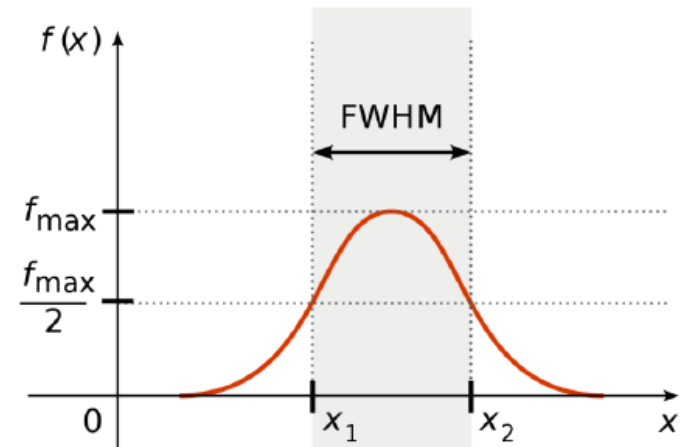
$$f_c^n(E_t) = \frac{1}{1 + \exp \left[\left(E_g + E_{en} + \frac{m_r^*}{m_e^*} E_t - F_c \right) / k_B T \right]}$$

$$f_v^m(E_t) = \frac{1}{1 + \exp \left[\left(E_{hm} - \frac{m_r^*}{m_h^*} E_t - F_v \right) / k_B T \right]}$$

Gain Spectrum

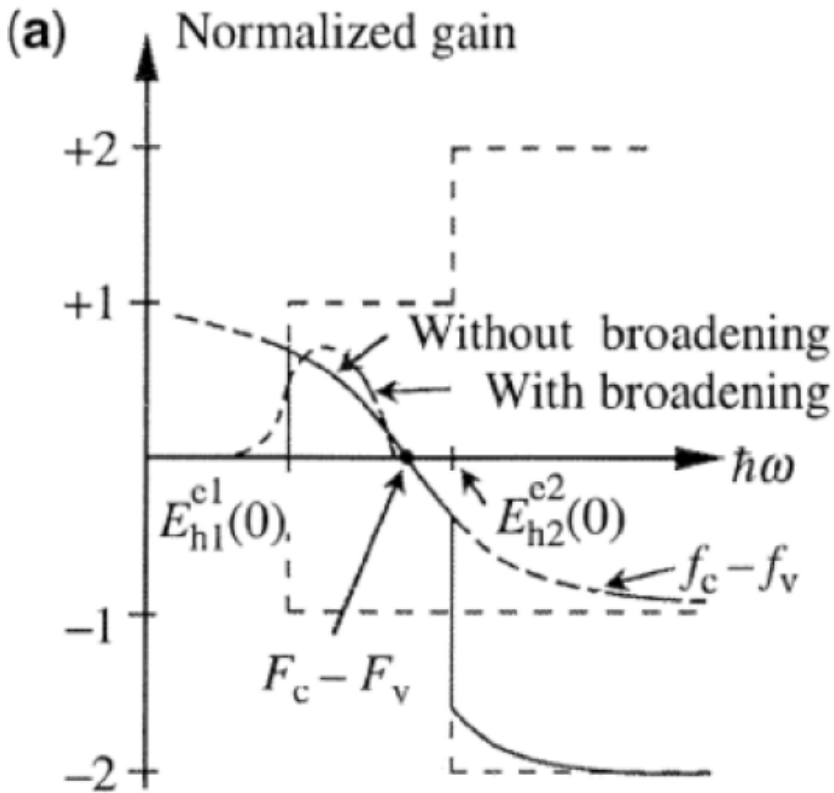
Linewidth Broadening Case

Full Width at Half Maximum (FWHM = 2γ)

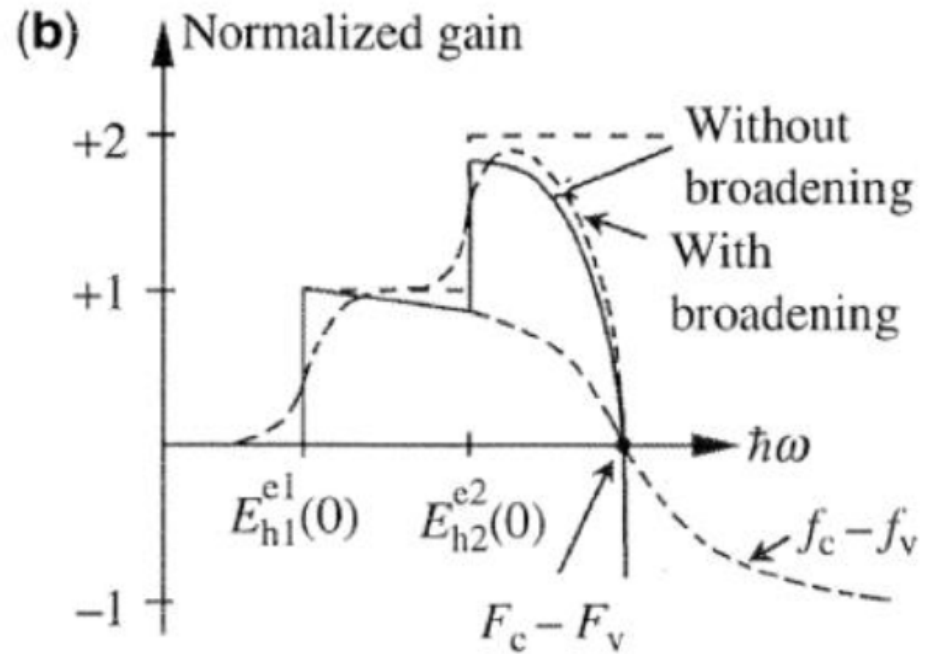


$$g(\hbar\omega) = C_0 \sum_{m,n} |I_{hm}^{en}|^2 \int_0^{\infty} dE_t \rho_r^{2D} |\hat{e} \cdot \mathbf{p}_{cv}|^2 \frac{\gamma / \pi}{[E_{hm}^{en} + E_t - \hbar\omega]^2 + \gamma^2} [f_c^n(E_t) - f_v^m(E_t)]$$

Gain Spectra with and without broadening



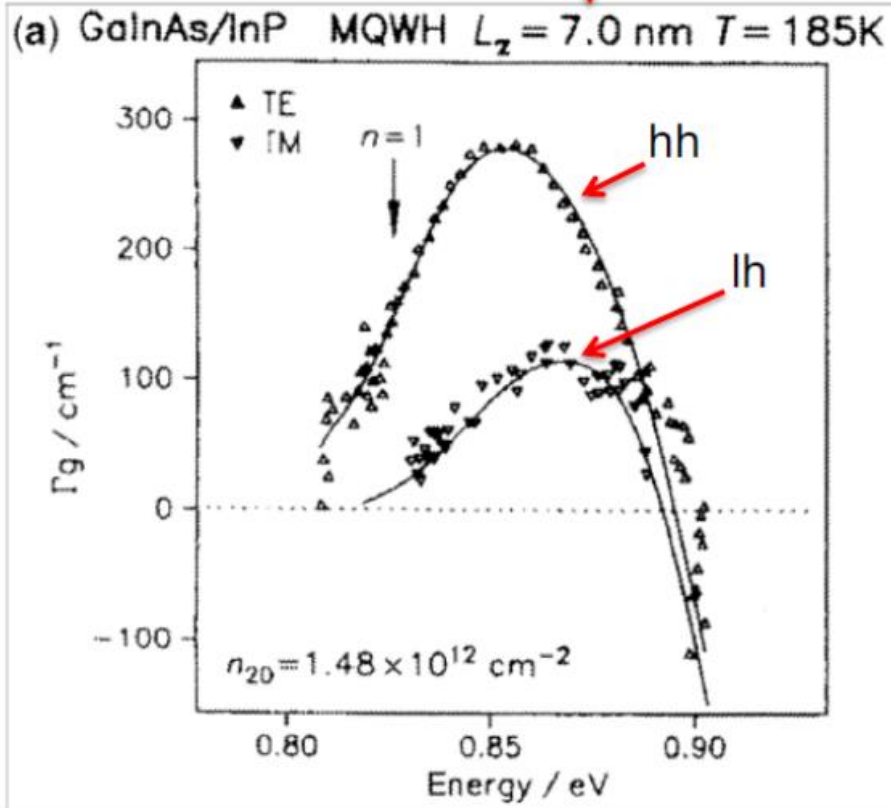
Transition involving one single electron and hole subband pair



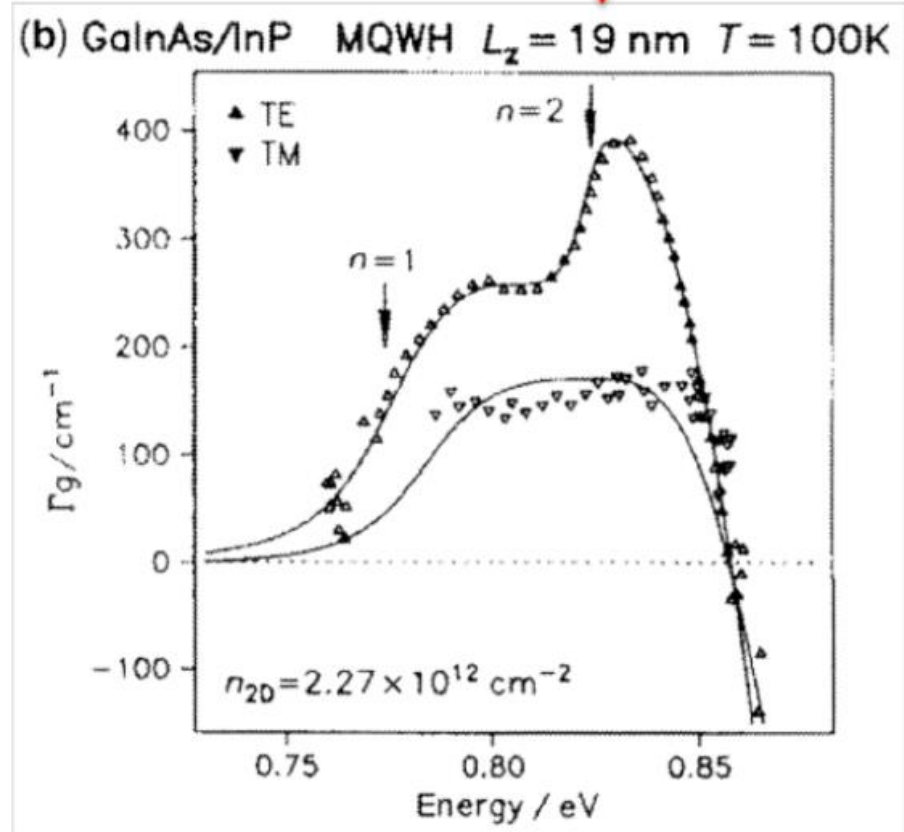
Transition involving two electron and two hole subbands

Comparison with experimental data

1-State



2-States

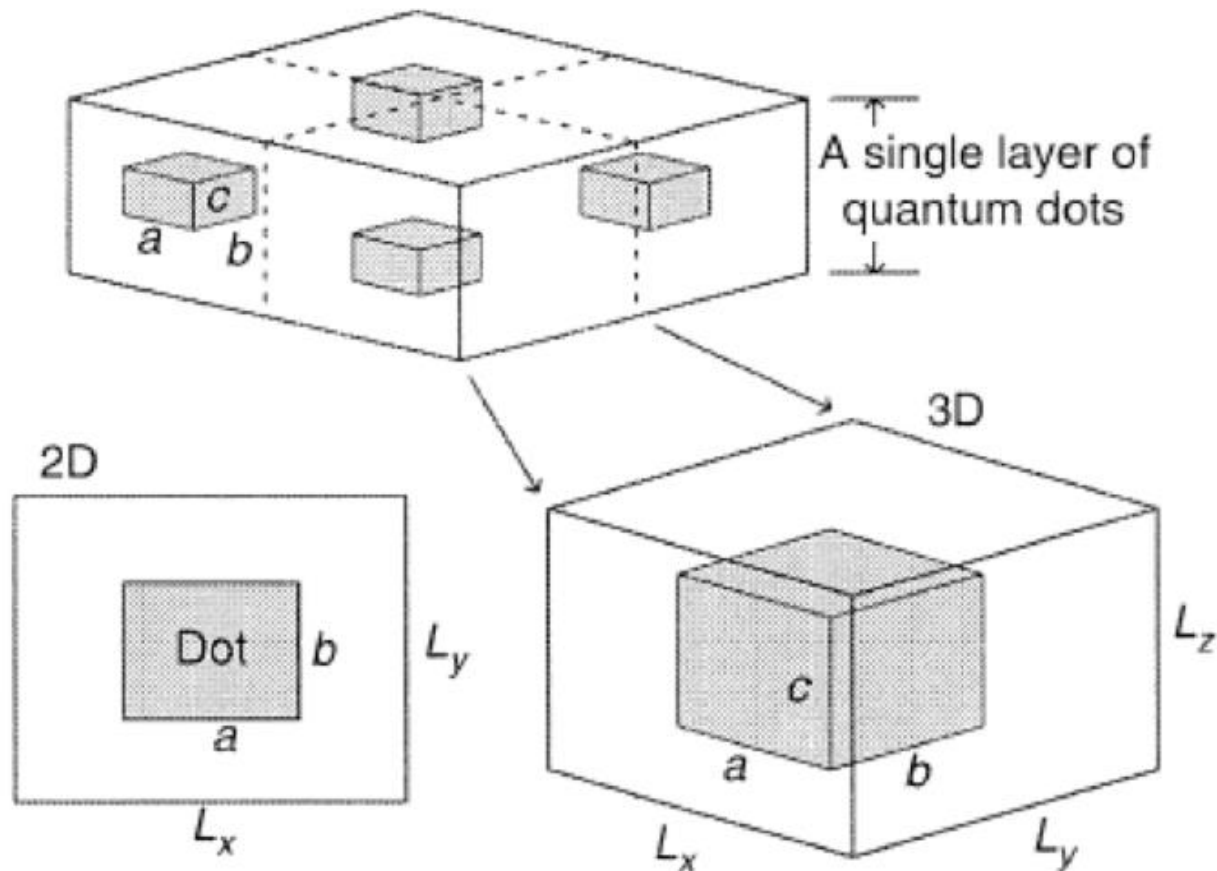


Zielinski *et al*, IEEE J. Quantum Electronics, QE-23, p.969 (1987).

Quantum Dots

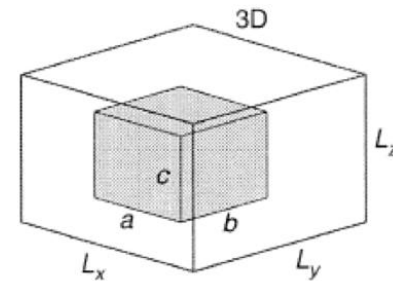
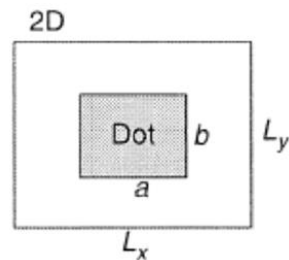
Ideal quantum dot assumptions

- Uniform dot size
- Uniform distribution



Ideal Quantum Dot – Wave functions and Energies

Dot Size $a \times b \times c$ Total Volume of Single Dot $V = L_x L_y L_z$



Dot Density $N_{dot}^{2D} = \frac{1}{L_x L_y}$

$$N_{dot}^{3D} = \frac{1}{V} = \frac{1}{L_x L_y L_z}$$

Fill Factor $F^{2D} = \frac{ab}{L_x L_y}$

$$F^{3D} = \frac{abc}{L_x L_y L_z}$$

Conduction Band – Wave functions and Energies

Wave Functions (Assume infinite barrier for simplicity)

$$\psi_c(x, y, z) = \frac{\sqrt{8}}{\sqrt{abc}} \sin\left(\frac{m\pi}{a}x\right) \sin\left(\frac{n\pi}{b}y\right) \sin\left(\frac{l\pi}{c}z\right) u_c(\mathbf{r})$$

Energy eigenvalues

$$E_c^{mnl} = E_{c0} + \frac{\hbar^2}{2m_e^*} \left[\left(\frac{m\pi}{a}\right)^2 + \left(\frac{n\pi}{b}\right)^2 + \left(\frac{l\pi}{c}\right)^2 \right]$$

Electron Density

$$n = \frac{2}{V} \sum_{m,n,l} f_c(E) = N_{dot}^{3D} 2 \sum_{m,n,l} f_c(E_c^{mnl}) = 2 \frac{N_{dot}^{2D}}{L_z} \sum_{m,n,l} \frac{1}{1 + e^{(E_c^{mnl} - F_c)/k_B T}}$$

Valence Band – Wave functions and Energies

Wave Functions (Assume infinite barrier for simplicity)

$$\psi_v(x, y, z) = \frac{\sqrt{8}}{\sqrt{abc}} \sin\left(\frac{m'\pi}{a}x\right) \sin\left(\frac{n'\pi}{b}y\right) \sin\left(\frac{l'\pi}{c}z\right) u_v(\mathbf{r})$$

Energy eigenvalues

$$E_v^{m'n'l'} = E_{v0} - \frac{\hbar^2}{2m_h^*} \left[\left(\frac{m'\pi}{a}\right)^2 + \left(\frac{n'\pi}{b}\right)^2 + \left(\frac{l'\pi}{c}\right)^2 \right]$$

Hole Density

$$p = \frac{2}{V} \sum_{m',n',l'} (1 - f_v(E)) = N_{dot}^{3D} 2 \sum_{m',n',l'} (1 - f_v(E_v^{m'n'l'})) = 2 \frac{N_{dot}^{2D}}{L_z} \sum_{m',n',l'} 1 - \frac{1}{1 + e^{(E_v^{m'n'l'} - F_v)/k_B T}}$$

$$p = 2 \frac{N_{dot}^{2D}}{L_z} \sum_{m',n',l'} \frac{1}{1 + e^{(F_v - E_v^{m'n'l'})/k_B T}}$$

Interband Absorption Spectrum

General expression

$$\alpha(\hbar\omega) = C_o \frac{2}{V} \sum_{\mathbf{k}} |\hat{\mathbf{e}} \cdot \mathbf{p}_{cv}|^2 \delta(E_c - E_v - \hbar\omega) (f_v - f_c)$$

Quantization in all dimensions \rightarrow sum over m, n, l

$$\alpha(\hbar\omega) = C_o \frac{2}{V} \sum_{m,n,l} \sum_{m',n',l'} |\langle \psi_c | \hat{\mathbf{e}} \cdot \mathbf{p} | \psi_v \rangle|^2 \delta(E_c^{mnl} - E_v^{m'n'l'} - \hbar\omega) (f_v - f_c)$$



$$\langle \psi_c | \hat{\mathbf{e}} \cdot \mathbf{p} | \psi_v \rangle \approx \langle u_c | \hat{\mathbf{e}} \cdot \mathbf{p} | u_v \rangle \delta_{mm'} \delta_{nn'} \delta_{ll'} = \hat{\mathbf{e}} \cdot \mathbf{p}_{cv} \delta_{mm'} \delta_{nn'} \delta_{ll'}$$

$$\rightarrow \alpha(\hbar\omega) = C_o \frac{2N_{dot}^{2D}}{L_z} \sum_{m,n,l} |\hat{\mathbf{e}} \cdot \mathbf{p}_{cv}|^2 \delta(E_c^{mnl} - E_v^{mnl} - \hbar\omega) (f_v - f_c)$$

with Interband Transition Energies


$$E_{cv}^{mnl} = E_c^{mnl} - E_v^{mnl} = E_g + \frac{\hbar^2}{2m_r^*} \left[\left(\frac{m\pi}{a} \right)^2 + \left(\frac{n\pi}{b} \right)^2 + \left(\frac{l\pi}{c} \right)^2 \right]$$

Absorption – Homogeneous Broadening

In case of no carrier injection, we can approximate $f_v = 1$ $f_c = 0$

For homogeneous broadening, the delta function can be replaced by a Lorentzian

$$\alpha_0(\hbar\omega) = C_0 \frac{2N_{dot}^{2D}}{L_z} \sum_{m,n,l} |\hat{e} \cdot \mathbf{p}_{cv}|^2 \underbrace{L(E_{cv}^{mnl} - \hbar\omega)}$$


$$L(E - \hbar\omega) = \frac{\gamma / \pi}{(E - \hbar\omega)^2 + \gamma^2}$$

With carrier injection

$$\alpha(\hbar\omega) = C_0 \frac{2N_{dot}^{2D}}{L_z} \sum_{m,n,l} |\hat{e} \cdot \mathbf{p}_{cv}|^2 L(E_{cv}^{mnl} - \hbar\omega) (f_v - f_c)$$

Absorption – Inhomogeneous Broadening

For uniform dots we had:
$$n = 2 \frac{N_{dot}^{2D}}{L_z} \sum_{m,n,l} f_c(E_c^{mnl})$$

In realistic case we will have variations of quantum dot size. Dot energy level become a Gaussian distribution with

$$G(E) = \frac{1}{\sqrt{2\pi}\sigma_c} e^{-\frac{(E-E_c^{mnl})^2}{2\sigma_c^2}} \quad \left\{ \begin{array}{l} \text{mean} = E_c^{mnl} \\ \text{FWHM} = 2\sqrt{2\ln 2}\sigma_c \approx 2.35\sigma_c \end{array} \right.$$

carrier density

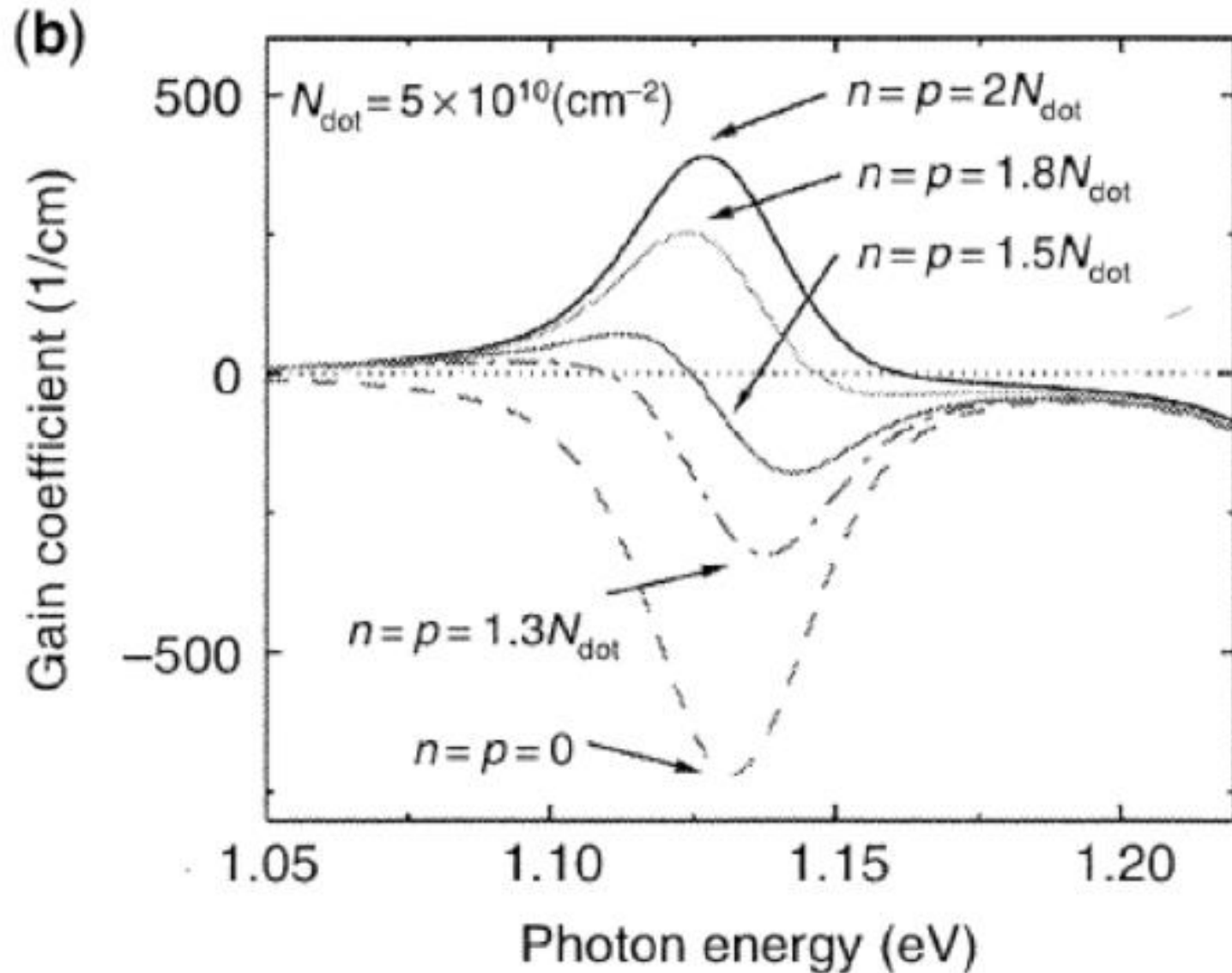
$$n = 2 \frac{N_{dot}^{2D}}{L_z} \sum_{m,n,l} \int_0^\infty dE G(E) f_c(E)$$

$$\alpha(\hbar\omega) = C_0 \sum_{m,n,l} \int_0^\infty dE |\hat{e} \cdot \mathbf{p}_{cv}|^2 D(E) L(E - \hbar\omega) (f_v - f_c)$$

$$D(E) = 2 \frac{N_{dot}^{2D}}{L_z} \frac{1}{\sqrt{2\pi}\sigma} e^{-\frac{(E-E_{cv}^{mnl})^2}{2\sigma^2}} \quad \sigma^2 = \sigma_c^2 + \sigma_v^2$$

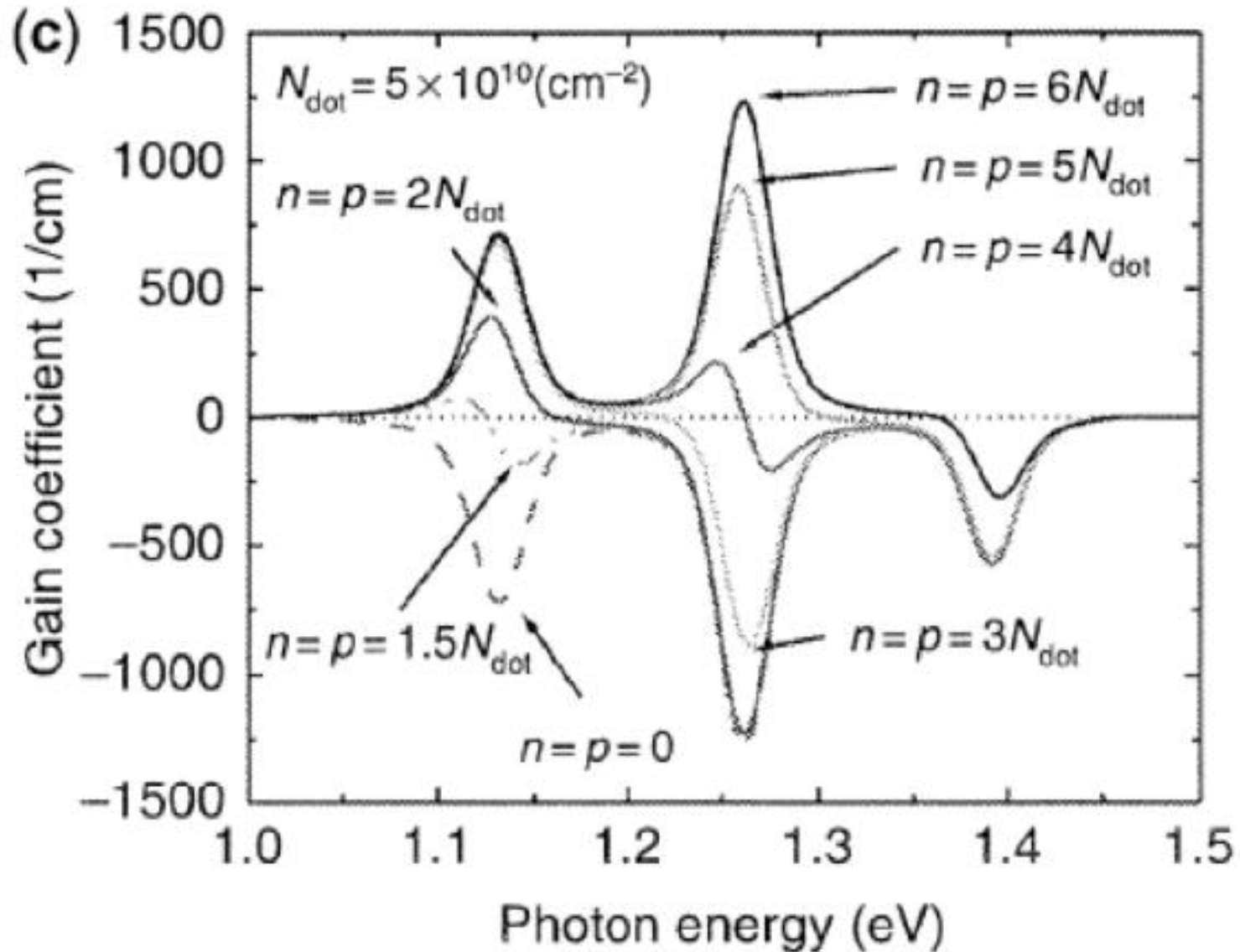
Examples = Homogeneous + Inhomogeneous Broadening

FWHM = 30 meV FWHM = 50 meV

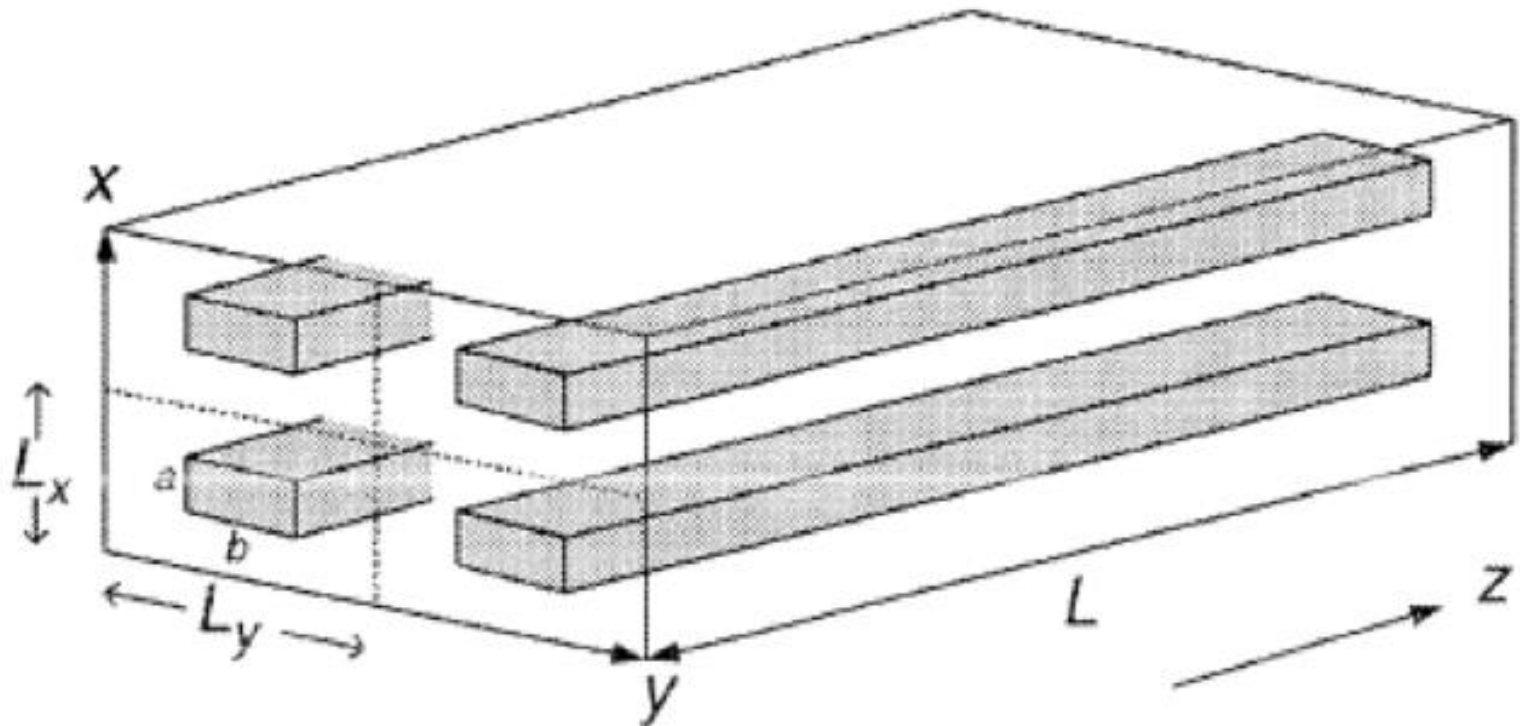


Examples = Homogeneous + Inhomogeneous Broadening

FWHM = 30 meV FWHM = 50 meV



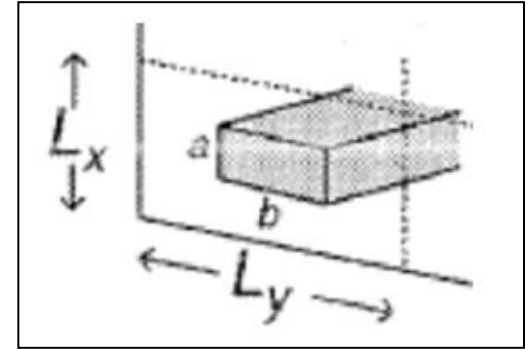
Quantum Wires



Ideal Quantum Wire – Wave functions and Energies

Areal Density in $x - y$ cross-section $N_{wr} = \frac{1}{L_x L_y}$

Fill Factor $F_{wr} = \frac{ab}{L_x L_y}$ Wire Length $L \gg a, b$



Wave Functions

$$\psi_c(x, y, z) = \frac{2}{\sqrt{ab}} \sin\left(\frac{m\pi}{a}x\right) \sin\left(\frac{n\pi}{b}y\right) \frac{1}{\sqrt{L}} e^{ik_z z} u_c(\mathbf{r})$$

$$\psi_v(x, y, z) = \frac{2}{\sqrt{ab}} \sin\left(\frac{m'\pi}{a}x\right) \sin\left(\frac{n'\pi}{b}y\right) \frac{1}{\sqrt{L}} e^{ik'_z z} u_v(\mathbf{r})$$

Energy eigenvalues

$$E_c^{mn}(k_z) = E_{c0} + \frac{\hbar^2}{2m_e^*} \left[\left(\frac{m\pi}{a}\right)^2 + \left(\frac{n\pi}{b}\right)^2 + k_z^2 \right]$$

$$E_v^{m'n'}(k'_z) = E_{v0} - \frac{\hbar^2}{2m_h^*} \left[\left(\frac{m'\pi}{a}\right)^2 + \left(\frac{n'\pi}{b}\right)^2 + k_z'^2 \right]$$

Density of States

Electron Density

$$n = \frac{2}{V} \sum_{m,n,k_z} f_c(E) = N_{wr} \frac{2}{L} \sum_{m,n} \int_{-\infty}^{\infty} \frac{dk_z}{\left(\frac{2\pi}{L}\right)} f_c(E)$$
$$= N_{wr} \int_0^{\infty} dE \rho_e^{1D}(E) f_c(E)$$

Density of state in a 1-D wire quantized along the x and y directions

$$\rho_e^{1D}(E) = \sum_{m,n} \frac{1}{\pi} \sqrt{\frac{2m_e^*}{\hbar^2}} \frac{1}{\sqrt{E - E_c^{mn}}} \quad \text{for } E > E_c^{mn}$$

Absorption coefficient

$$\alpha(\hbar\omega) = C_0 N_{wr} \sum_{m,n} |\hat{e} \cdot \mathbf{p}_{cv}|^2 \rho_r^{1D}(\hbar\omega - E_c^{mn})(f_v - f_c)$$

joint density of states

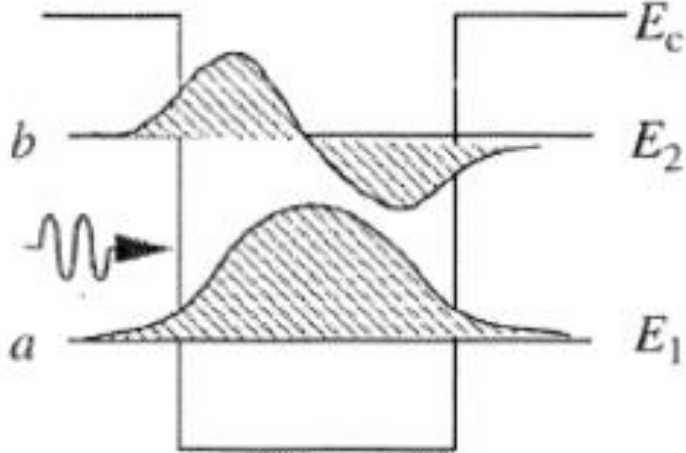
$$\rho_r^{1D}(\hbar\omega - E_c^{mn}) = \frac{1}{\pi} \sqrt{\frac{2m_r^*}{\hbar^2}} \frac{1}{\sqrt{\hbar\omega - E_c^{mn}}}$$

$$E_{cv}^{mn} = E_g + \frac{\hbar^2}{2m_r^*} \left[\left(\frac{m\pi}{a} \right)^2 + \left(\frac{n\pi}{b} \right)^2 \right]$$

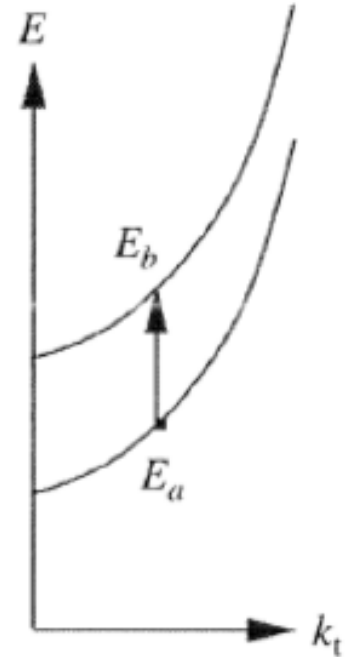
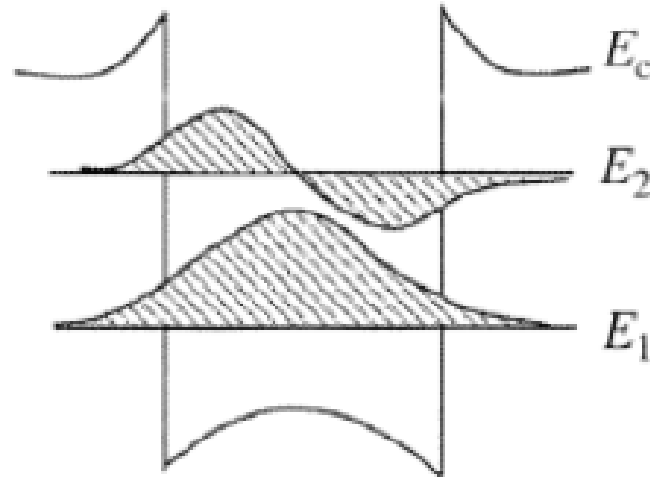
Intersubband Absorption

Transition between ground state and first excited state

Single QW = Low doping



Modulation doped QW



$$\psi_a(\mathbf{r}) = u_c(\mathbf{r}) \frac{e^{i\mathbf{k}_t \cdot \boldsymbol{\rho}}}{\sqrt{A}} \phi_1(z)$$

$$\psi_b(\mathbf{r}) = u_{c'}(\mathbf{r}) \frac{e^{i\mathbf{k}'_t \cdot \boldsymbol{\rho}}}{\sqrt{A}} \phi_2(z)$$

transverse momenta

$$\mathbf{k}_t = k_x \hat{x} + k_y \hat{y}$$

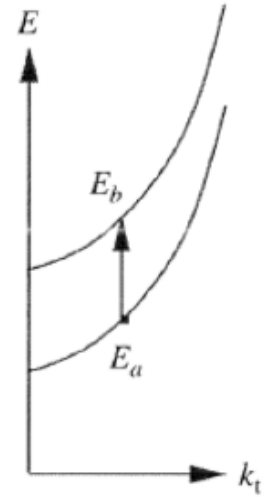
$$\mathbf{k}'_t = k'_x \hat{x} + k'_y \hat{y}$$

position vector

$$\boldsymbol{\rho} = x\hat{x} + y\hat{y}$$

Intersubband Absorption Spectrum

initial state $E_a = E_1 + \frac{\hbar^2 k_t^2}{2m_e^*}$ **final state** $E_b = E_1 + \frac{\hbar^2 k_t^2}{2m_e^*}$



$$\alpha(\hbar\omega) = \left(\frac{\omega}{n_r c \epsilon_0} \right) \frac{2}{V} \sum_{\mathbf{k}_t} \sum_{\mathbf{k}'_t} \frac{|\hat{\mathbf{e}} \cdot \boldsymbol{\mu}_{ba}|^2 \gamma}{(E_b - E_a - \hbar\omega)^2 + \gamma^2} (f_a - f_b)$$

$$= \left(\frac{\omega}{n_r c \epsilon_0} \right) \frac{|\boldsymbol{\mu}_{21}|^2 \gamma}{(E_2 - E_1 - \hbar\omega)^2 + \gamma^2} \frac{2}{V} \sum_{\mathbf{k}_t} (f_a - f_b) = \left(\frac{\omega}{n_r c \epsilon_0} \right) \frac{|\boldsymbol{\mu}_{21}|^2 \gamma}{(E_2 - E_1 - \hbar\omega)^2 + \gamma^2} (N_1 - N_2)$$

intersubband dipole moment

$$\boldsymbol{\mu}_{21} = \langle \phi_2 | e\mathbf{z} | \phi_1 \rangle = \int \phi_2^*(z) e\mathbf{z} \phi_1(z) dz$$

electrons per unit volume in nth subband

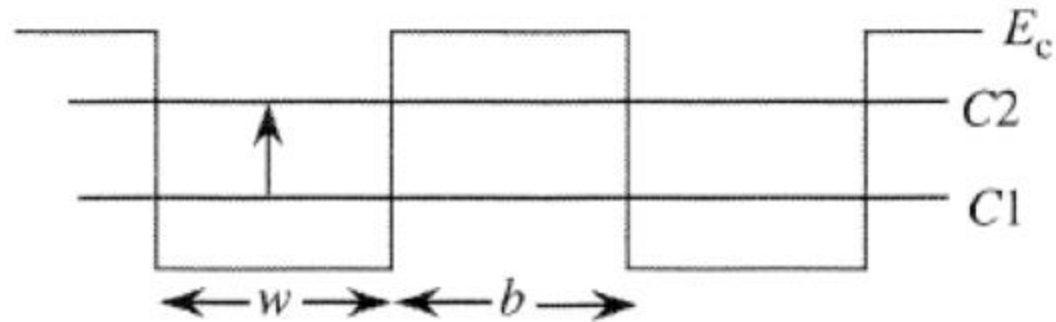
$$N_n = \frac{m_e^* k_B T}{\pi \hbar^2 L_z} \ln \left[1 + e^{(E_F - E_n)/k_B T} \right]$$

low temperature $(E_F - E_n) \gg k_B T$

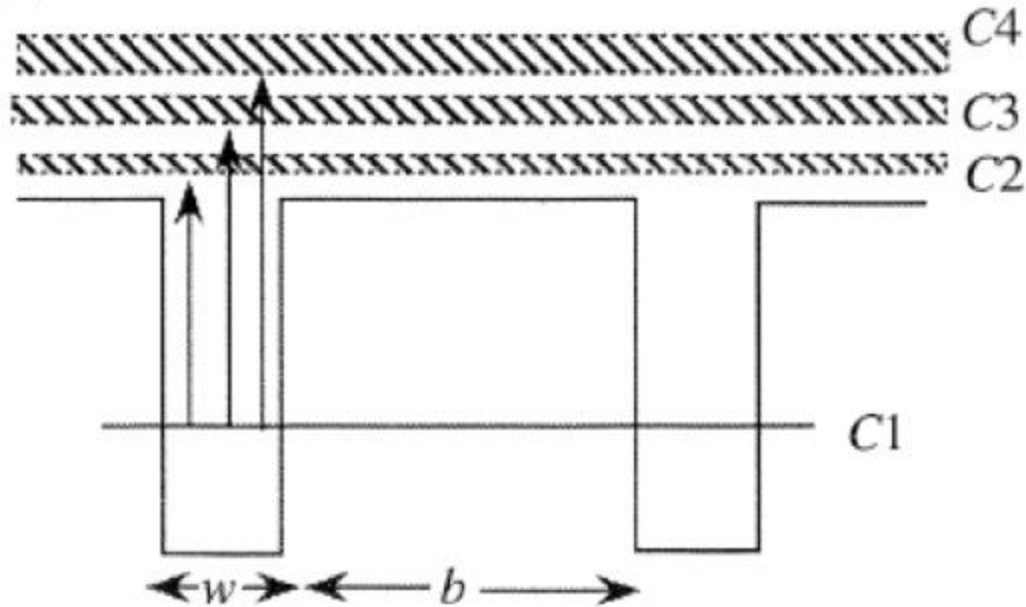
$$N_n = \frac{m_e^*}{\pi \hbar^2 L_z} (E_F - E_n)$$

Absorption in a Superlattice

(a) Bound-to-bound transition



(b) Bound-to-continuum miniband transitions



Intersubband Absorption Spectrum

Using the se two previous results

$$\alpha(\hbar\omega) = \left(\frac{\omega}{n_r c \mathcal{E}_0} \right) \frac{|\mu_{21}|^2 \gamma}{(E_2 - E_1 - \hbar\omega)^2 + \gamma^2} (N_1 - N_2)$$

$$N_n = \frac{m_e^*}{\pi \hbar^2 L_z} (E_F - E_n)$$

considering two levels occupied

$$\alpha(\hbar\omega) = \left(\frac{\omega}{n_r c \mathcal{E}_0} \right) \frac{|\mu_{21}|^2 \gamma}{(E_2 - E_1 - \hbar\omega)^2 + \gamma^2} \left(\frac{m_e^*}{\pi \hbar^2 L_z} \right) (E_2 - E_1)$$

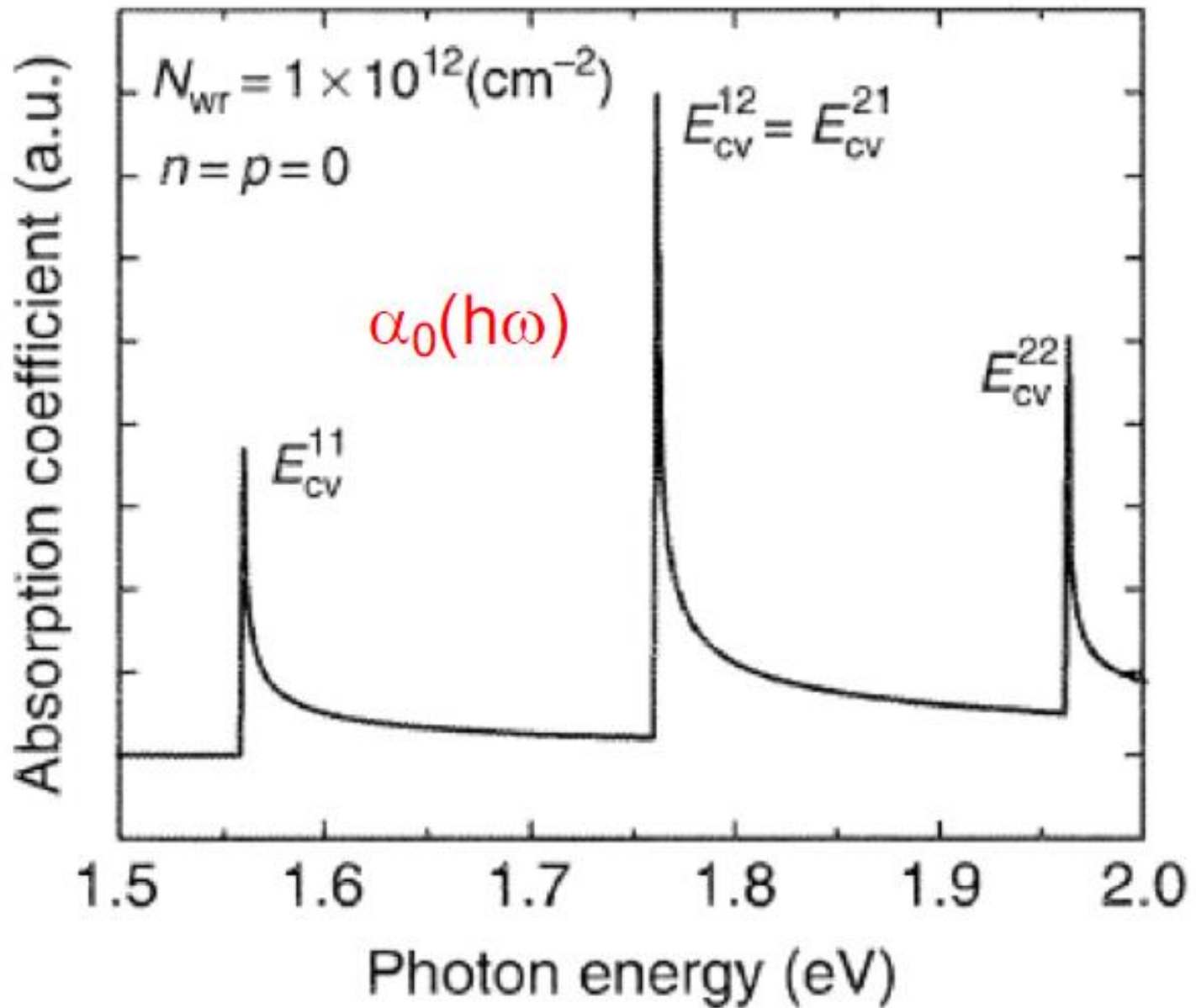
INTEGRATED ABSORBANCE

$$A = \int_0^{\infty} \alpha(\hbar\omega) d(\hbar\omega) \simeq \left(\frac{\omega_{21}}{n_r c \mathcal{E}_0} \right) |\mu_{21}|^2 \pi (N_1 - N_2)$$

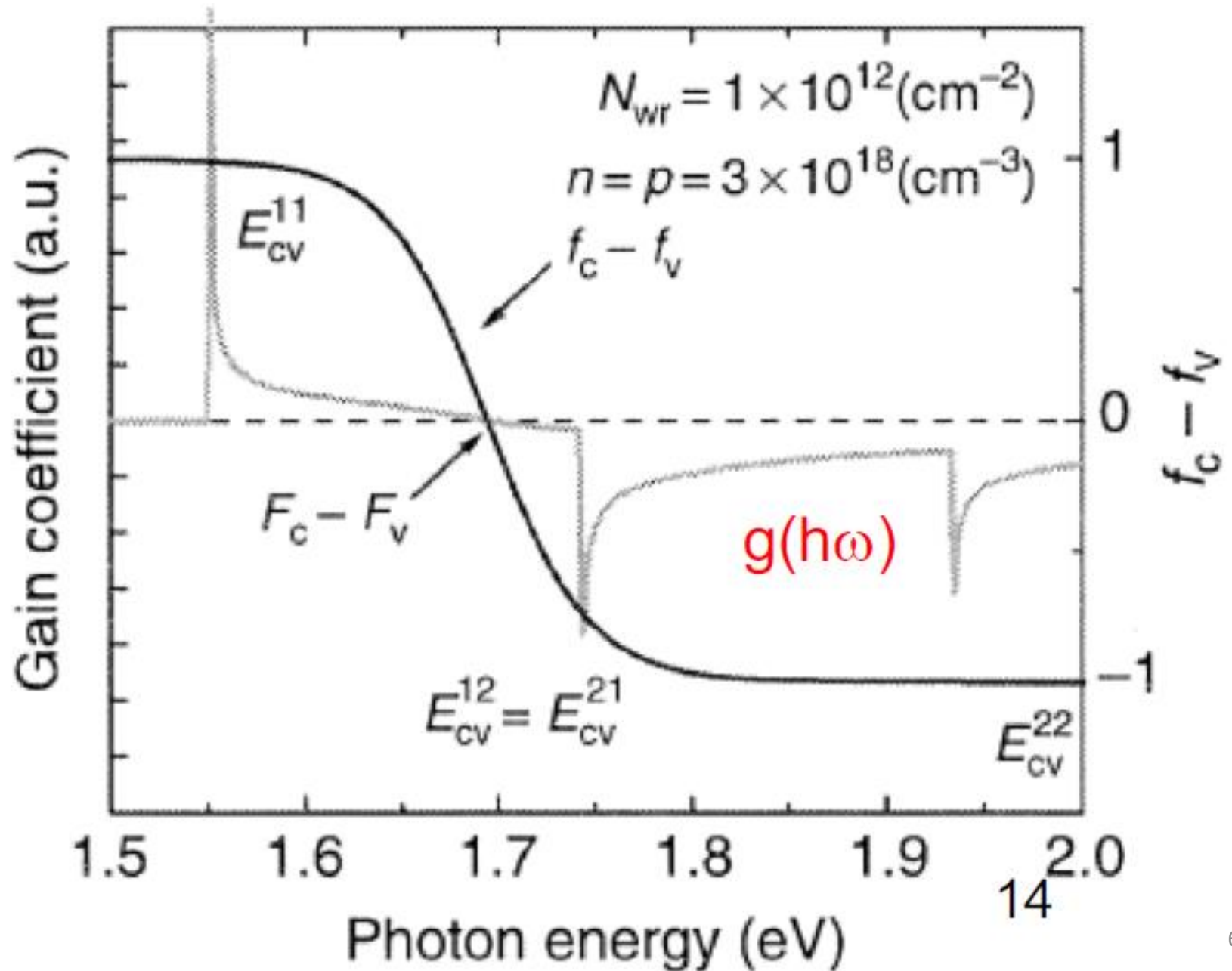
Reading Assignments:

Sections 9.3 and 9.4 of Chuang's book

Absorption coefficient



Gain coefficient



Two-dimensional quantum confinement in quantum-wire (QWR) semiconductor lasers is expected to yield improved static and dynamic performance compared to conventional quantum-well (QW) lasers.^{1,2} The improved features include very low threshold currents (in the microampere regime), reduced temperature sensitivity, higher modulation bandwidth, and narrower spectral linewidth.